

EZ-PD™ CCG7D Automotive USB dual-port Type-C with PD and buck-boost controller

General description

EZ-PD™ CCG7D is a highly integrated dual-port USB Type-C Power Delivery (PD) solution with integrated buck-boost controllers. It complies with the latest USB Type-C and PD specifications, and is targeted for automotive applications such as infotainment head unit charger, rear seat chargers as well as rear seat entertainment. Integration offered by EZ-PD™ CCG7D not only reduces the bill-of-materials (BOM) but also provides a footprint optimized solution for automotive charging needs. It also includes hardware-controlled protection features on the VBUS. EZ-PD™ CCG7D supports a wide input voltage range (4 V–24 V with 40-V tolerance) and programmable switching frequency (150 kHz–600 kHz) in an integrated PD solution.

EZ-PD™ CCG7D is the most programmable USB PD solution with an on-chip 32-bit Arm® Cortex®-M0 processor, 128-KB flash, 16-KB RAM, and 32-KB ROM that leaves most flash available for user application use. It also includes various analog and digital peripherals such as ADC, PWMs, and timers. The inclusion of a fully programmable MCU with analog and digital peripherals allows the implementation of custom system management functions such as power throttling, load sharing, temperature monitoring, and fault logging.

Applications

- Head unit charger
- Rear seat charger (RSC)
- Rear seat entertainment (RSE)

Features

- USB PD
 - Supports two USB PD ports
 - Supports USB PD Revision 3.2 including programmable power supply (PPS) mode
 - Extended data messaging
- Type-C
 - Configurable resistors RP and RD
 - VBUS provider NFET gate driver
 - Integrated 100-mW VCONN power supply and control
- 2× buck-boost controller
 - 150 to 600 kHz switching frequency
 - 5.5 to 24 V input, 40-V tolerant
 - 3.3 to 21.5 V output
 - 20-mV voltage and 50-mA current steps for PPS
 - Supports selectable pulse-skipping mode (PSM) and forced continuous current/conduction mode (FCCM)
 - Supports soft start
 - Programmable spread spectrum frequency modulation for low EMI
 - Programmable phase shift across two ports to further reduce the EMI
- 2× legacy/proprietary charging blocks
 - Supports QC 2.0/3.0/4.0/5.0, Apple charging 2.4A, Samsung adaptive fast charging (AFC), USB BC 1.2

Features

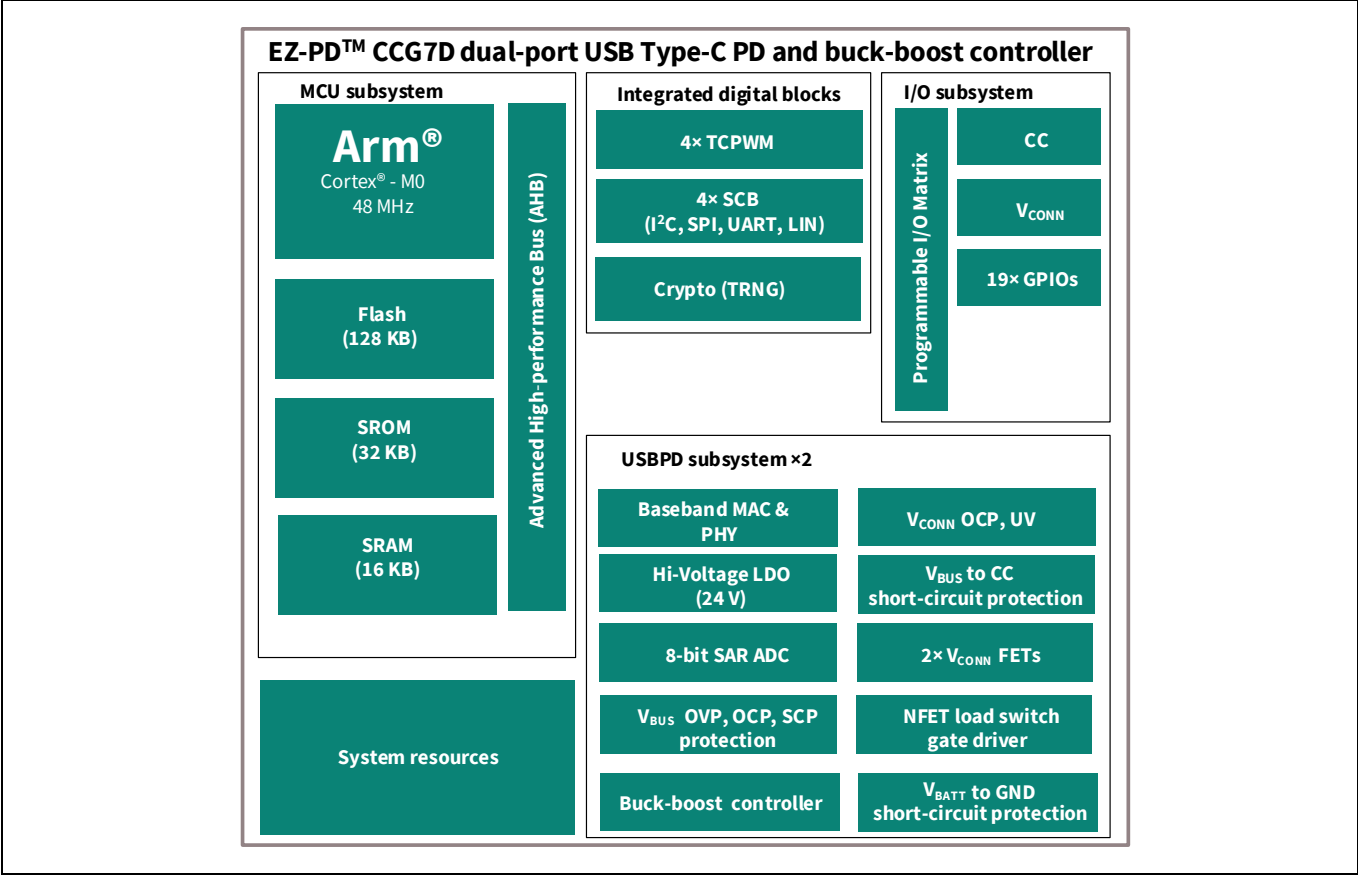
- System-level fault protection
 - On-chip VBUS overvoltage protection (OVP), overcurrent protection (OCP), undervoltage protection (UVP)
 - VBUS to CC short protection
 - VBAT to GND protection FET gate driver
 - Undervoltage lockout (UVLO)
 - Supports overtemperature protection through integrated ADC circuit and internal temperature sensor
 - Supports connector and board temperature measurement using external thermistors
- 32-bit MCU subsystem
 - 48-MHz Arm® Cortex®-M0 CPU
 - 128-KB flash
 - 16-KB SRAM
 - 32-KB ROM
- Peripherals and GPIOs
 - 19 GPIOs
 - Two overvoltage GPIOs
 - 3× 8-bit ADC
 - 4× 16-bit timer/counter/PWMs (TCPWM)
- Communication interfaces
 - 4× SCBs (I²C/SPI/UART/LIN)
- Clocks and oscillators
 - Integrated oscillator eliminating the need for an external clock
- Power supply
 - 4 to 24 V input (40-V tolerant)
 - 3.3 to 21.5 V output
 - Integrated LDO capable of 5 V at 150 mA
- Packages
 - 68-pin QFN, wettable flank, AEC-Q100
 - Supports automotive ambient temperature range (–40°C to +105°C) with 125°C operating junction temperature

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Logic block diagram

Logic block diagram



Functional block diagram

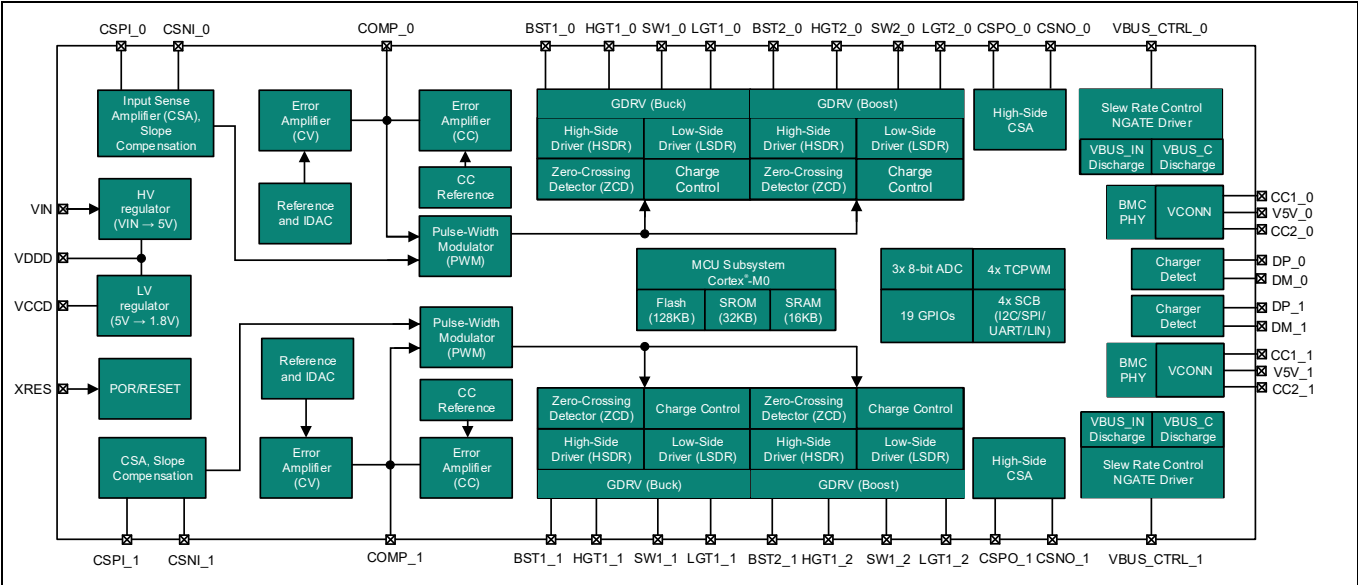


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1 Functional overview

1.1 MCU subsystem

1.1.1 CPU

The Cortex®-M0 in EZ-PD™ CCG7D devices is a 32-bit MCU, which is optimized for low-power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. It also includes a hardware multiplier, which provides a 32-bit result in one cycle. It includes an interrupt controller (the NVIC block) with 32 interrupt inputs and a wakeup interrupt controller (WIC), which can wake the processor up from Deep Sleep mode.

1.1.2 Flash ROM and SRAM

EZ-PD™ CCG7D devices have 128-KB flash and 32-KB ROM for non-volatile storage. ROM stores libraries for authentication and device drivers such as I²C, SPI, and so on. That spares flash for user application. Flash provides the flexibility to store code for any customer feature and allows firmware upgrades to meet the latest USB PD specifications and application needs.

The 16-KB RAM is used under software control to store the temporary status of system variables and parameters. A supervisory ROM that contains boot and configuration routines is provided.

1.2 USBPD subsystem

This subsystem provides the interface to the Type-C USB port. This subsystem comprises:

- USB PD physical layer
- VCONN switches and 100 mW VCONN source
- UVP, OVP on VBUS
- Output high-side current sense amplifier (CSA) for VBUS
- VBUS discharge control
- Gate driver for VBUS provider NFET
- Charger detection block for legacy charging (for example: BC1.2, Apple charging, and so on)
- VBAT to ground short-circuit protection
- VBUS to CC short-circuit protection

1.2.1 USB PD physical layer

The USBPD subsystem contains the USB PD physical layer block and supporting circuits. The USB PD physical layer consists of a transmitter and receiver that communicate BMC encoded data over the CC channel per the PD 3.2 standard. All communication is half-duplex. The physical layer or PHY implements collision avoidance to minimize communication errors on the channel.

The USBPD block includes all termination resistors (Rp and Rd) and their switches as required by the USB Type-C specification. Rp and Rd resistors are required to implement connection detection, plug orientation detection and for the establishment of the USB source/sink roles. The Rp resistor is implemented as a current source.

EZ-PD™ CCG7D device family with accompanying firmware is fully complaint with Revisions 3.2 and 2.0 of the USB PD specification. The device supports PPS operation at all valid voltages from 3.3 to 21 V.

EZ-PD™ CCG7D devices support Rp under HW control in unconnected (standby) state to minimize standby power.

EZ-PD™ CCG7D devices support USB PD Extended Messages containing data of up to 260 bytes. The extended messages are larger than expected by USB PD 2.0 hardware. As per the USB PD protocol specification, devices compliant with USB PD Revision 3.0 and later implement a chunking mechanism; messages are limited to Revision 2.0 sizes unless both source and sink confirm and negotiate compatibility with longer message lengths.

1.2.2 VCONN switches

EZ-PD™ CCG7D's internal LDO voltage regulator is capable of powering a 100 mW VCONN supply for electronically marked cable assemblies (EMCA), VCONN-powered devices (VPD), and VCONN-powered accessories (VPA) as defined in the USB Type-C specification. All circuitry including VCONN switches and OCP is integrated in the device. In the event the VCONN current exceeds the VCONN OCP limit, EZ-PD™ CCG7D can be configured to shut down the Type-C port after a certain number of user configurable retries. The port can be re-enabled after a physical disconnect.

1.2.3 VBUS UVP and OVP

VBUS undervoltage and overvoltage faults are monitored using internal resistor dividers. The fault thresholds and response times are user configurable. See [EZ-PD™ Configuration Utility](#) for more details. In the event of a UVP or OVP, EZ-PD™ CCG7D can be configured to shut down the Type-C port after a certain number of user configurable retries. The port can be re-enabled after a physical disconnect.

1.2.4 VBUS OCP and SCP

VBUS overcurrent and short-circuit faults are monitored using internal current sense amplifiers. Similar to OVP and UVP, the OCP and SCP fault thresholds and response times are configurable as well. See [EZ-PD™ Configuration Utility](#) for more details. In the event of OCP or SCP, EZ-PD™ CCG7D can be configured to shut down the Type-C port after a certain number of user configurable retries. The port can be re-enabled after a physical disconnect.

1.2.5 High-side CSA for VBUS

EZ-PD™ CCG7D device family supports VBUS current measurement and control using an external resistor (5 mΩ) in series with the VBUS path. The voltage drop across this resistor is used to measure the average output current. The same resistor is also used to sense and precisely control the output current in the PPS current foldback mode of operation.

1.2.6 VBUS discharge control

The chip supports high-voltage (21.5 V) VBUS discharge circuitry. Upon the detection of device disconnection, faults, or hard resets, the chip will discharge the output VBUS terminals to vSafe5V and/or vSafe0V within the time limits specified in the USB PD Specification.

1.2.7 Gate driver for VBUS provider NFET

EZ-PD™ CCG7D devices have an integrated high-voltage gate driver to drive the gate of an external high-side NFET on the VBUS provider path. The gate driver drives the load switch that controls the connection between VBUS_IN and VBUS_C. VBUS_CTRL is the output of this gate driver. To turn off the external NFET, the gate driver drives VBUS_IN low to 0 V. To turn on the external NFET, it drives the gate to VBUS_IN + 8 V. There is an optional slow turn-on feature which reduces the high-current spikes on the output. For a typical gate capacitance of 3 nF, a slow turn-on time of 2 ms to 10 ms is configurable using firmware.

1.2.8 Legacy charge detection and support

CG7D implements battery charger emulation and detection (source and sink) for USB BC.1.2, legacy Apple charging, Qualcomm Quick Charge 2.0/3.0, and Samsung AFC protocols.

1.2.9 VBAT to ground short protection

EZ-PD™ CCG7D devices can protect against high currents through the Type-C return (ground) path. A NFET and a current sense resistor are placed in series with the ground return path from the Type-C connector as shown in **Figure 1**. This resistor senses the current, and if it exceeds the firmware-configured threshold, the NFET is turned off to interrupt the current. This protects against overcurrent conditions caused by external faults (for example, if the Type-C connector ground is accidentally connected to the car's battery). The current sense can be implemented with either a single-ended connection (referenced to internal ground) or with a true differential connection (see CSN connection in **Figure 1**). The differential connection provides better current measurement accuracy but uses an extra pin that can otherwise be repurposed as a GPIO. In the event of VBAT to ground short protection, EZ-PD™ CCG7D can be configured to shut down the series FET between the Type-C receptacle ground and the system ground. The recovery and retry mechanism can be customized using application firmware.

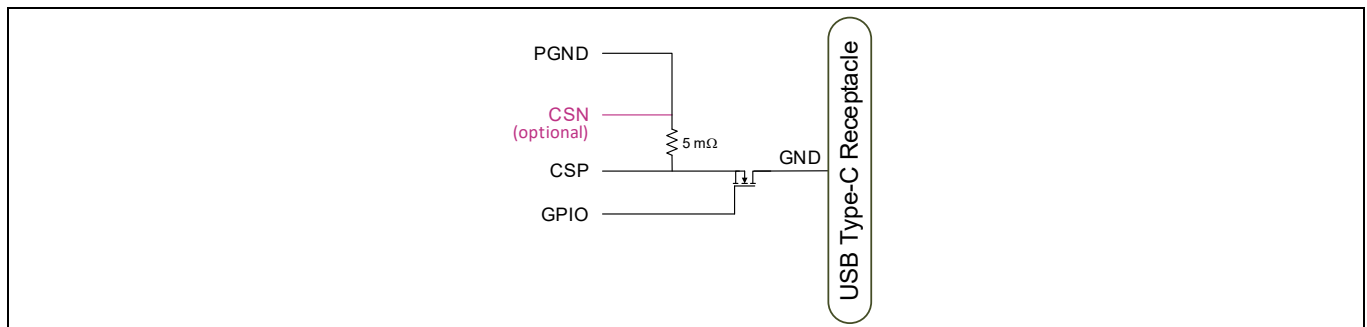


Figure 1 VBUS to ground short circuit protection

1.2.10 VBUS to CC short protection

EZ-PD™ CCG7D's CC pins have integrated protection from accidental shorts to high-voltage VBUS and VBAT. EZ-PD™ CCG7D devices can handle up to 24 V external voltage on its CC pins without damage. In the event an overvoltage is detected on the CC pin, EZ-PD™ CCG7D can be configured to shut down the Type-C port completely. The port will resume normal operation once the CC voltage detected is within normal range.

1.3 Buck-boost subsystem

The buck-boost subsystem in EZ-PD™ CCG7D devices can be configured to operate in buck-boost mode, buck-only mode or boost-only mode. While buck-boost mode requires four external switching FETs, buck-only and boost-only modes require only two FETs. Buck-only mode is useful when EZ-PD™ CCG7D device's port is used for USB Type-A only applications. **Figure 2** shows the buck-boost subsystem's main external components and connections.

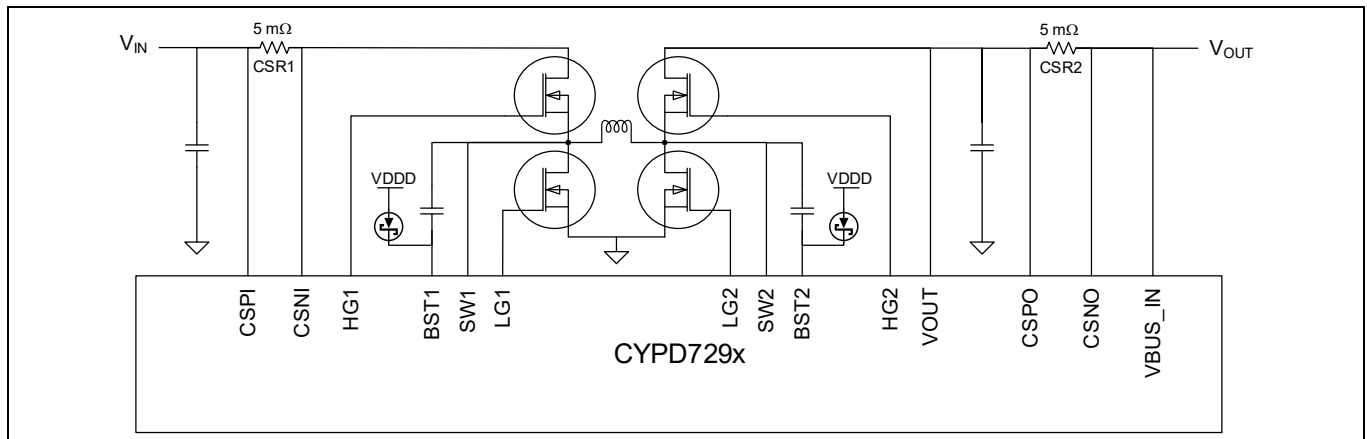


Figure 2 Buck-boost schematic showing external components

Buck-boost subsystem in EZ-PD™ CCG7D devices have the following key functional blocks:

- High-side (cycle-by-cycle) CSA
- High-side and low-side gate driver
- Pulse width modulator (PWM)
- Error amplifier (EA)

1.3.1 High-side (cycle-by-cycle) CSA

EZ-PD™ CCG7D device's buck-boost controller implements peak current control in both boost and buck modes. A high-side CSA is used for peak current sensing through an external resistor (5 mΩ; see CSR1 in **Figure 2**) placed in series with the buck control FET. This current sense amplifier has a high bandwidth and a very wide common mode range. This current sense resistor is connected to the CSA block through pins CSPI and CSNI as shown in **Figure 2**. This block implements slope compensation to avoid sub-harmonic oscillation for the internal current loop. In addition to peak current sensing, it provides a current limit comparator for shutting off the buck-boost converter if the current hits an upper threshold which is programmable.

1.3.2 High-side gate driver and low-side gate driver

EZ-PD™ CCG7D's buck-boost controller provides four N-channel MOSFET gate drivers: two floating high-side gate drivers at the HG1 and HG2 pins, and two ground referenced low-side drivers at the LG1 and LG2 pin. The high-side gate drivers drive the high-side external FET with a nominal VGS of 5 V. The high-side gate driver has a programmable drive strength to drive external FET. An external capacitor and Schottky diode form a bootstrap network to collect and store the high voltage source ($V_{IN} + \sim 5\text{ V}$ for HG1 and $V_{BUS} + \sim 5\text{ V}$ for HG2) needed to drive the high-side FET.

The low-side gate driver drives the low-side external FET with a nominal VGS of 5 V using energy sourced from EZ-PD™ CCG7D's internal LDO regulator and stored in the capacitor between PVDD and PGND. Low-side gate driver has programmable drive strength to drive external FET.

In addition to drive strength, the high-side gate driver and the low-side gate driver have programmable options for deadtime control and zero-crossing levels. High-side gate driver and low-side gate driver blocks include zero-crossing detector (ZCD) to implement discontinuous-conduction mode (DCM) mode with diode emulation. The gate drivers for the switching FETs function at their nominal drive voltage levels (5 V) provided the VIN voltage is between 5.5 V and 24 V.

1.3.3 Error amplifier (EA)

EZ-PD™ CCG7D's buck-boost controller contains two error amplifiers for output voltage and current regulation. The error amplifier is a trans-conductance type amplifier with single compensation pin (COMP) to ground for both the voltage and current loops. In voltage regulation, the output voltage is compared with the internal reference voltage and the output of EA is fed to the PWM block. In current regulation, the average current is sensed by VBUS high-side current sense amplifier through the external resistor. The output of the VBUS CSA is compared with an internal reference in error amplifier block and EA output is fed to the PWM block. EZ-PD™ CCG7D's firmware configures and controls the integrated programmable error amplifier circuit for achieving the required VBUS voltage output from the power section.

1.3.4 Pulse width modulator (PWM)

EZ-PD™ CCG7D device family's PWM block generates the control signals for the gate drivers driving the external FETs in peak current mode control. There are many programmable options for minimum/maximum pulse width, minimum/maximum period, frequency and pulse skip levels to optimize the system design.

EZ-PD™ CCG7D devices have two firmware-selectable operating modes to optimize efficiency and reduce losses under light load conditions: PSM and FCCM.

1.3.5 Pulse-skipping mode (PSM)

In pulse-skipping mode, the controller reduces the total number of switching pulses without reducing the active switching frequency by working in "bursts" of normal nominal-frequency switching interspersed with intervals without switching. The output voltage thus increases during a switching burst and decreases during a quiet interval. This mode results in minimal losses at the cost of higher output voltage ripple. When in this mode, EZ-PD™ CCG7D devices monitor the voltage across the buck or boost sync FET to detect when the inductor current reaches zero; when this occurs, the EZ-PD™ CCG7D devices switch off the buck or boost sync FET to prevent reverse current flow from the output capacitors (that is, diode emulation mode). Several parameters of this mode are programmable through firmware, allowing the user to strike their own balance between light load efficiency and output ripple.

1.3.6 Forced-continuous-conduction mode (FCCM)

In FCCM, the nominal switching frequency is maintained at all times, with the inductor current going below zero (that is, "backwards" or from the output to the input) for a portion of the switching cycle as necessary to maintain the output voltage and current. This keeps the output voltage ripple to a minimum at the cost of light-load efficiency.

1.4 Buck-boost controller operation regions

The input-side CSA's output is compared with the output of the error amplifier to determine the pulse width of the PWM. PWM block compares the Input voltage and output voltage to determine the buck, boost, and buck-boost regions. The switching time/period of the four gate drivers (HG1, LG1, HG2, LG2) depends upon the region in which the block is operating as well as the mode such as DCM or FCCM. The exact V_{in} vs V_{out} thresholds for transitions into and out of each region are adjustable in firmware including the hysteresis.

1.4.1 Buck region operation ($V_{IN} \gg V_{BUS}$)

When the V_{IN} voltage is significantly higher than the required V_{BUS} voltage, EZ-PD™ CCG7D devices operate in the buck region. In this region, the boost side FETs are inactivated, with the boost control FET (connected to LG2) turned off and the boost sync FET (connected to HG2) turned on. The buck side FETs are controlled as a buck converter with synchronous rectification as shown in [Figure 3](#).

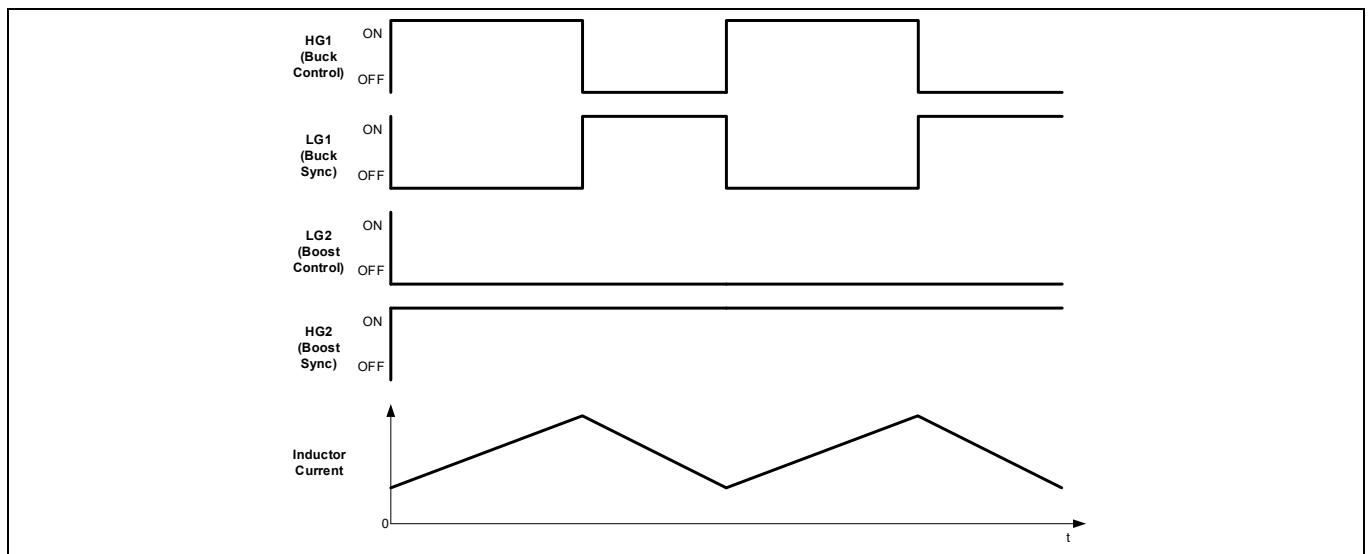


Figure 3 Buck operation waveforms

1.4.2 Boost region operation ($V_{IN} \ll V_{BUS}$)

When the V_{IN} voltage is significantly lower than the required V_{BUS} voltage, EZ-PD™ CCG7D devices operate in the boost region. In this region, the buck side FETs are inactivated, with the sync FET turned off and the buck control FET turned on. The boost side FETs are controlled as a boost converter with synchronous rectification as shown in [Figure 4](#).

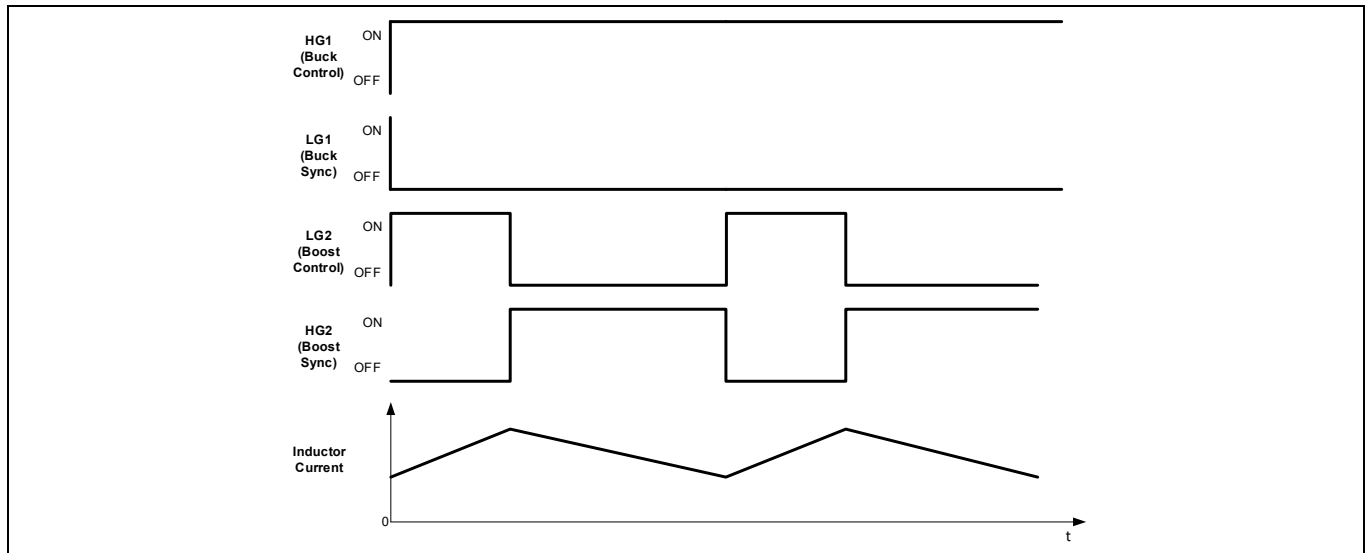


Figure 4 Boost operation waveforms

1.4.3 Buck-boost region 1 operation ($V_{IN} \sim V_{BUS}$)

When the V_{IN} voltage is slightly higher than the required V_{BUS} voltage, EZ-PD™ CCG7D devices operate in the buck-boost region 1. In this region, the boost side works at a fixed 20% duty cycle (programmable) while the buck side (LG1 / HG1) duty cycle is modulated to control the output voltage. All four FETs are switching every cycle in this operating region as shown in [Figure 5](#).

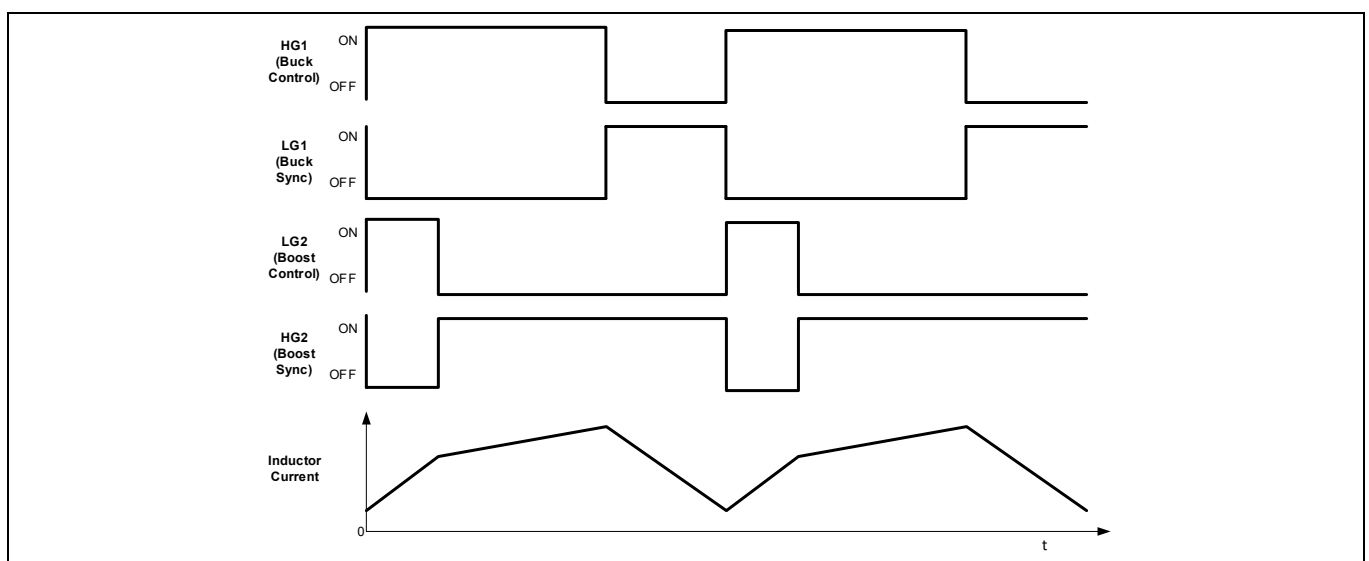


Figure 5 Buck-boost region 1 ($V_{IN} \sim V_{BUS}$) operation waveforms

1.4.4 Buck-boost region 2 operation ($V_{IN} \sim < V_{BUS}$)

When the V_{IN} voltage is slightly lower than the required V_{BUS} voltage, EZ-PD™ CCG7D devices operate in the buck-boost region 2. In this region, the buck side works at a fixed 80% duty cycle (programmable) while the boost side (LG2) duty cycle is modulated to control the output voltage. All four FETs are switching every cycle in this operating region as shown in [Figure 6](#).

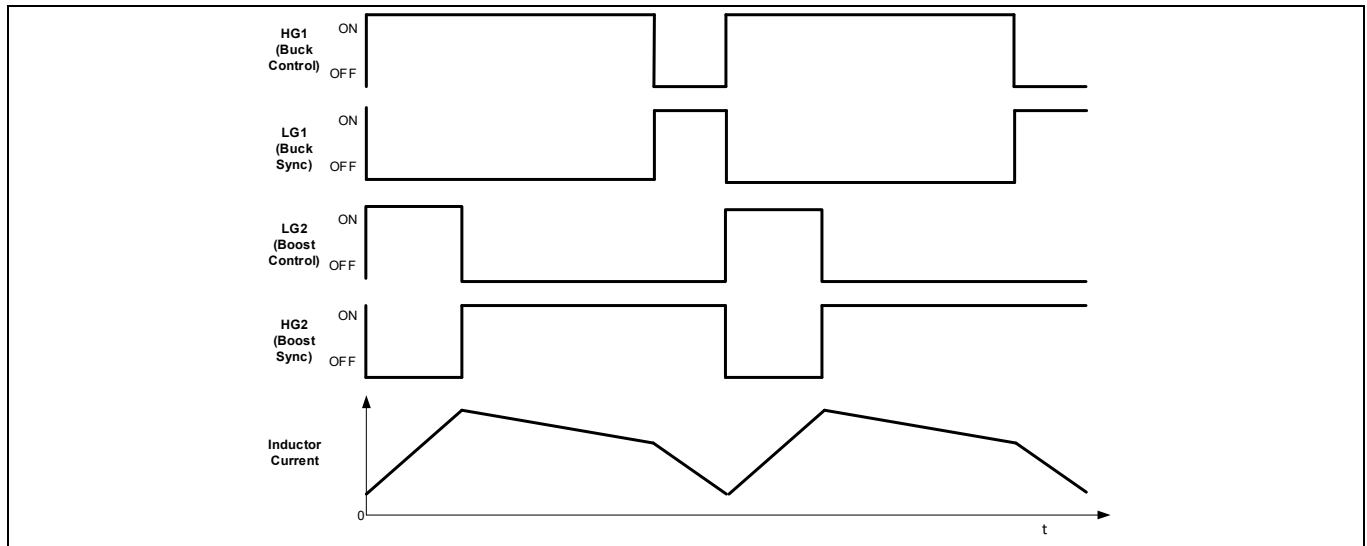


Figure 6 Buck-boost region 2 ($V_{IN} \sim < V_{BUS}$) operation waveforms

1.4.5 Switching frequency and spread spectrum

EZ-PD™ CCG7D devices offer programmable switching frequency between 150 kHz and 600 kHz. The controller supports spread spectrum clocking within the operating frequency range in all operating modes. Spread spectrum is essential for charging applications to meet EMC/EMI requirements by spreading emissions caused by switching over a wide spectrum instead of a fixed frequency, thereby reducing the peak energy at any particular frequency. Both the switching frequency and the spread spectrum span are firmware programmable.

1.5 Analog blocks

1.5.1 ADC

EZ-PD™ CCG7D devices family has three 8-bit SAR ADCs available for general purpose analog-to-digital conversion applications in the chip. The ADCs can be accessed from the GPIOs through an on-chip analog mux. See [Table 30](#) for detailed specs on the ADCs.

1.6 Integrated digital blocks

1.6.1 Serial communication block (SCB)

EZ-PD™ CCG7D devices have four SCB blocks that can be configured for I²C, SPI, UART or LIN. These blocks implement full multi-master and slave I²C interfaces capable of multi-master arbitration. This I²C implementation is compliant with the standard [NXP I2C Specification V3.0](#). These blocks operate at speeds of up to 1 Mbps and have flexible buffering options to reduce interrupt overhead and latency for the CPU. The SCB blocks support 8-byte deep FIFOs for Receive and Transmit, which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time. The I²C port I/Os for SCB0 are overvoltage tolerant (OVT). The I²C ports for SCB1-3 are not OVT tolerant.

1.6.2 Timer, counter, pulse-width modulator (TCPWM)

The TCPWM block of EZ-PD™ CCG7D devices support four timers or counters or pulse-width modulators. These timers are available for internal timer use by firmware or for providing PWM-based functions on the GPIOs.

1.7 I/O subsystem

The EZ-PD™ CCG7D devices have 19 GPIOs including the I²C and SWD pins which can also be used as GPIOs. The GPIO block implements the following:

- Eight output drive modes
 - Input only
 - Weak pull-up with strong pull-down
 - Strong pull-up with weak pull-down
 - Open drain with strong pull-down
 - Open drain with strong pull-up
 - Strong pull-up with strong pull-down
 - Disabled
 - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTTL)
- Individual control of input and output disables
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode)
- Selectable slew rates for dV/dt related noise control
- OVT on one pair of GPIOs

During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix (HSIOM) is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals such as USB Type-C port are also fixed in order to reduce internal multiplexing complexity. Data output registers and pin state register store, respectively, the values to be driven on the pins and the states of the pins themselves. The configuration of the pins can be done by the programming of registers through software for each digital I/O port.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it.

The I/O ports can retain their state during Deep Sleep mode or remain ON. If the operation is restored using reset, then the pins shall go the High-Z state. If operation is restored by an interrupt event, then the pin drivers shall retain their state until firmware chooses to change it. The IOs (on data bus) do not draw current on power down.

1.8 System resources

1.8.1 Watchdog timer (WDT)

EZ-PD™ CCG7D devices have a watchdog timer running from the internal low-speed oscillator (ILO). This allows watchdog operation during Deep Sleep and generate a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register.

1.8.2 Reset

EZ-PD™ CCG7D devices can be reset from a variety of sources including a Software Reset. Reset events are asynchronous and guarantee reversion to a known state. The Reset cause is recorded in a Register, which is sticky through Reset and allows software to determine the cause of the reset. XRES pin is the dedicated pin for reset to apply hardware reset.

1.8.3 Clock system

EZ-PD™ CCG7D devices have a fully integrated clock with no external crystal required. EZ-PD™ CCG7D device's clock system is responsible for providing clocks to all sub-systems that require clocks (SCB and PD) and for switching between different clock sources, without glitches.

The HFCLK signal can be divided down as shown to generate synchronous clocks for the digital peripherals. The clock dividers have 8-bit, 16-bit and 16-bit fractional divide capability. The 16-bit capability allows a lot of flexibility in generating fine-grained frequency values. The clock dividers generate either enabled clocks (that is, 1 in N clocking where N is the divisor) or an approximately 50% duty cycle clock (exactly 50% for even divisors, one clock difference in the high and low values for odd divisors).

In [Figure 7](#), PERXYZCLK represents the clocks for different peripherals.

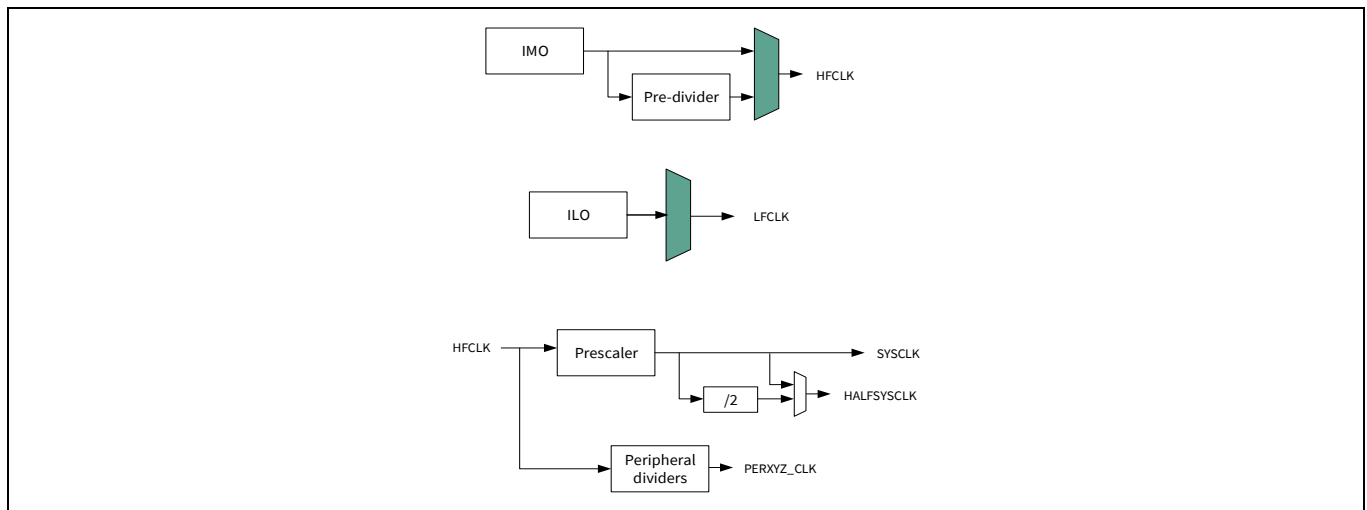


Figure 7 Clocking architecture of EZ-PD™ CCG7D devices

1.8.4 Internal main oscillator (IMO) clock source

The IMO is the primary source of internal clocking in EZ-PD™ CCG7D devices. IMO default frequency for EZ-PD™ CCG7D devices is 48 MHz $\pm 2\%$.

1.8.5 ILO clock source

The internal low-speed oscillator is a very low power, relatively inaccurate, oscillator, which is primarily used to generate clocks for peripheral operation in USB suspend (Deep Sleep) mode.

2 Power subsystem

Figure 8 shows an overview of the power subsystem architecture for EZ-PD™ CCG7D devices. The power subsystem of EZ-PD™ CCG7D devices operate from VIN supply which can vary from 4 V to 24 V. The VDDD pin, the output of 5 V LDO gets input from VIN supply. The VDDD pin can also be used as a power supply for external loads up to 150 mA. EZ-PD™ CCG7D devices have two different power modes: Active and Deep Sleep, transitions between which are managed by the power system. The VCCD pin, the output of the core (1.8 V) regulator, is brought out for connecting a 0.1-μF capacitor for the regulator stability only. This pin is not supported as a power supply for external load.

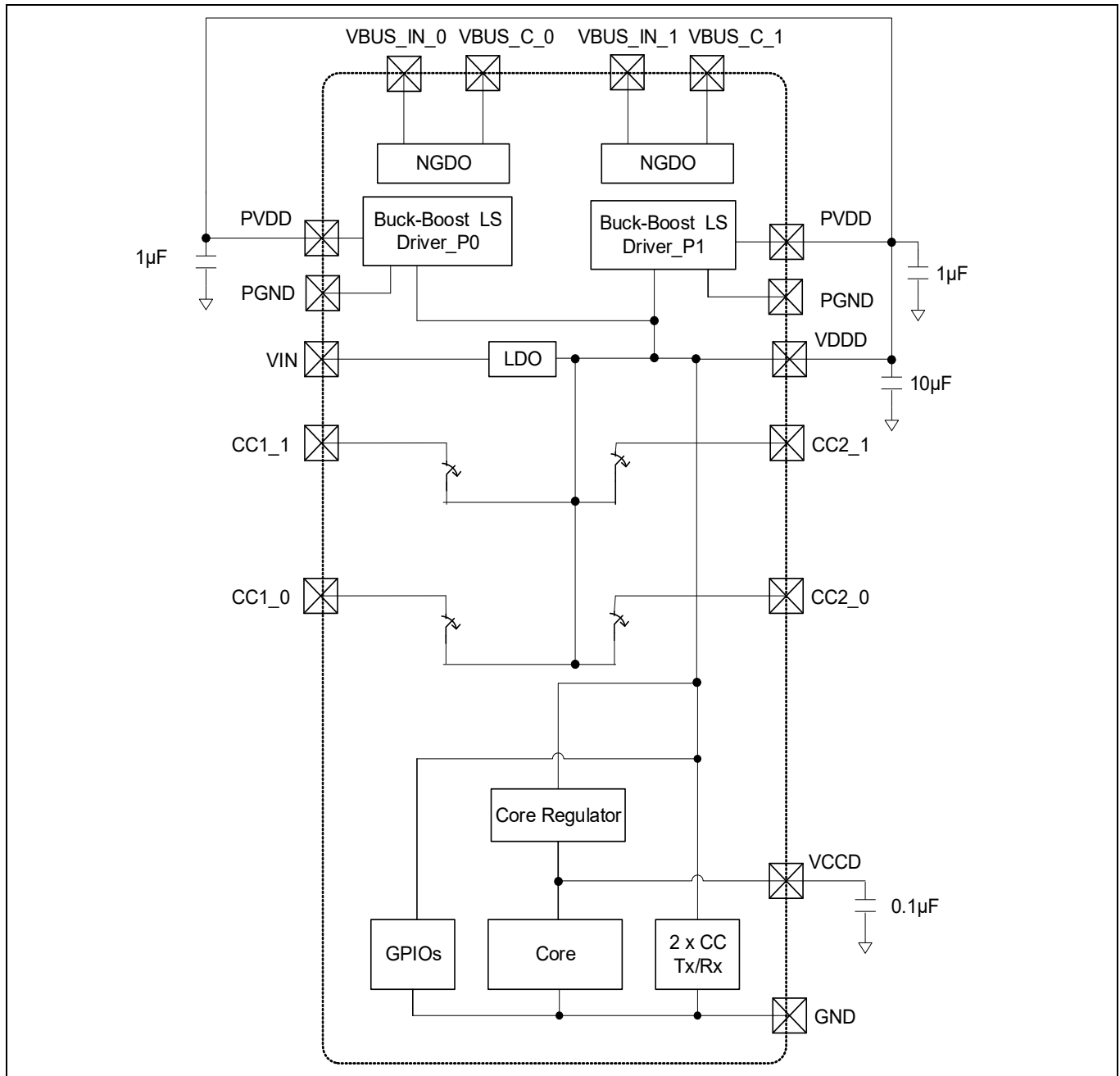


Figure 8 Power system requirement block diagram

2.1 VIN undervoltage lockout (UVLO)

EZ-PD™ CCG7D supports UVLO to allow the device to shut down when the input voltage is below the reliable level. It guarantees predictable behavior when the device is up and running.

2.2 Using external VDDD supply

By default, external VDDD is not supported for EZ-PD™ CCG7D devices. However, usage of external VDDD supply can be enabled using firmware. The pre-requisite for enabling external forcing of VDDD is to always maintain Vin higher than VDDD and the external load on VDDD pin of EZ-PD™ CCG7D devices should never be higher than prescribed load capability of internal VDDD LDO.

2.3 Power modes

Table 1 lists the power modes of the device accessible and observable by the user.

Table 1 Power modes

| Mode | Description |
|------------|---|
| RESET | Power is valid and XRES is not asserted. An internal reset source is asserted or sleep controller is sequencing the system out of reset |
| ACTIVE | Power is valid and CPU is executing instructions |
| SLEEP | Power is valid and CPU is not executing instructions. All logic that is not operating is clock gated to save power |
| DEEP SLEEP | Main regulator and most hard-IP are shut off. Deep Sleep regulator powers logic, but only low-frequency clock is available |
| XRES | Power is valid and XRES is asserted. Core is powered down |

3 Pin list

Table 2 EZ-PD™ CCG7D pinout table

| Pin# | Pin name | GPIO port assignment | Description |
|------|-------------|----------------------|---|
| 1 | SW1_0 | – | Negative power rail of port 0 buck high-side gate driver. This is also connected to one input terminal of zero current detection of buck low-side gate driver. Connect to the switch node (inductor) on the buck (input) side. Use a short and wide trace to minimize the inductance and resistance of this connection. |
| 2 | LG1_0 | | Buck low-side gate driver output of Port 0. Connect to the buck (input) side sync (low side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 3 | PGND_0 | | Ground of low-side gate driver of Port 0. This is also connected to one input terminal of zero current detection (ZCD) of buck low-side gate driver. Connect directly to Port 0's board ground plane. |
| 4 | PVDD_0 | | Supply of low-side gate driver of Port 0. Connect to VDDD. Use 1 μ F and 0.1 μ F bypass capacitors as close to the EZ-PD™ CCG7D IC as possible. |
| 5 | LG2_0 | | Boost low-side gate driver output of Port 0. Connect to the boost (output) side control (low side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 6 | VOUT_0 | | Output of the buck-boost converter of Port 0. This is also connected to one input terminal of reverse current protection (RCP) of Boost high-side gate driver. Connect to the boost sync (high side) FET's drain. Use a dedicated (Kelvin) trace for this connection. |
| 7 | SW2_0 | | Negative power rail of Port 0 boost high-side gate driver. This is also connected to one input terminal of RCP of boost high-side gate driver. Connect to the switch node (inductor) on the boost (output) side. Use a short and wide trace to minimize the inductance and resistance of this connection. |
| 8 | HG2_0 | | Boost high-side gate driver output of Port 0. Connect to the boost (output) side sync (high side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 9 | BST2_0 | | Boosted power supply of Port 0 boost high-side gate driver. Bootstrap capacitor node. Connect Schottky diode from VDDD to BST2_0. Also, connect a bootstrap capacitor from this pin to SW2_0. |
| 10 | COMP_0 | | EA output pin of Port 0. Connect a compensation network to GND. Contact Infineon for assistance in designing the compensation network. |
| 11 | CSPO_0 | | Positive input of output current sensing amplifier of Port 0. Connect to positive terminal of the output current sense resistor. |
| 12 | CSNO_0 | | Negative input of output current sensing amplifier of Port 0. Connect to negative terminal of the output current sense resistor. |
| 13 | VBUS_IN_0 | | Input of feedback voltage of error amplifier of Port 0. Connect to the VBUS node between the output current sense resistor and the VBUS provider NFET. |
| 14 | VBUS_C_0 | | Type-C connector VBUS voltage of Port 0. Connect to the Type-C connector's VBUS pin. |
| 15 | CC1_0 | | Type-C connector configuration channel 1 of Port 0. Connect directly to the CC1 pin on the port's Type-C connector. Also connect a 390-pF capacitor to ground. |
| 16 | CC2_0 | | Type-C connector configuration channel 2 of Port 0. Connect directly to the CC2 pin on the port's Type-C connector. Also connect a 390-pF capacitor to ground. |
| 17 | VBUS_CTRL_0 | | VBUS NFET gate driver output of Port 0. Connect to the provider NFET's gate. |
| 18 | CSN_0_GPIO0 | P0.0 | GPIO / negative input terminal of Port 0's VBAT – GND protection circuit. Connect to the negative terminal of the VBAT – GND short protection current sense resistor. |
| 19 | CSP_0_GPIO1 | P0.1 | GPIO/ positive input terminal of Port 0's VBAT – GND protection circuit. Connect to the positive terminal of the VBAT – GND short protection current sense resistor. |

Pin list

Table 2 EZ-PD™ CCG7D pinout table (continued)

| Pin# | Pin name | GPIO port assignment | Description |
|------|--------------|----------------------|--|
| 20 | GPIO2 | P0.2 | GPIO. This GPIO is pulled-down during reset/power-up, as it is used to disable the FET for the Vbat to GND short circuit protection for Port 0. Set the correct drive mode, if the Vbat to GND short circuit protection is not required in the design. |
| 21 | GPIO3 | P0.3 | GPIO |
| 22 | GPIO4 | P0.4 | |
| 23 | DP_0_GPIO5 | P1.0 | USB D+ of Port 0 / GPIO: D+ for implementing BC 1.2, AFC, QC or Apple charging. EZ-PD™ CCG7D does not support USB data transmission on this pin. |
| 24 | DM_0_GPIO6 | P1.1 | USB D- of Port 0 / GPIO: D- for implementing BC 1.2, AFC, QC or Apple charging. EZ-PD™ CCG7D does not support USB data transmission on this pin. |
| 25 | VDDD | – | 5-V LDO output. Connect a 1-μF ceramic bypass capacitor to this pin. Also, connect this pin directly to pin 63. |
| 26 | DM_1_GPIO7 | P1.2 | USB D- of port 1/GPIO: D- for implementing BC 1.2, AFC, QC or Apple charging. EZ-PD™ CCG7D does not support USB data transmission on this pin. |
| 27 | DP_1_GPIO8 | P1.3 | USB D+ of port 1/ GPIO: D+ for implementing BC 1.2, AFC, QC or Apple charging. EZ-PD™ CCG7D does not support USB data transmission on this pin. |
| 28 | XRES | – | External reset – Active low. Contains a 3.5 KΩ to 8.5 KΩ internal pull-up. |
| 29 | GPIO9 | P2.0 | GPIO |
| 30 | GPIO10 | P2.1 | |
| 31 | GPIO11 | P1.4 | GPIO. This GPIO is pulled-down during reset/power-up, as it is used to disable the FET for the Vbat to GND short circuit protection for Port 1. Set the correct drive mode, if the Vbat to GND short circuit protection is not required in the design. |
| 32 | CSP_1_GPIO12 | P1.5 | GPIO / positive terminal of low-side current sense amplifier (LS CSA) of Port 1. Connect to the positive terminal of the VBAT – GND short protection current sense resistor. |
| 33 | CSN_1_GPIO13 | P1.6 | GPIO / negative terminal of low-side CSA of Port 1. Connect to the negative terminal of the VBAT – GND short protection current sense resistor. |
| 34 | GND | – | Chip ground. Connect directly to the exposed pad (EPAD) and to pin 64. |
| 35 | VBUS_CTRL_1 | | VBUS NFET gate driver output of Port 1. Connect to the provider NFET's gate. |
| 36 | CC2_1 | | Type-C connector configuration channel 2 of Port 1. Connect directly to the CC2 pin on the port's Type-C connector. Also connect a 390-pF capacitor to ground. |
| 37 | CC1_1 | | Type-C connector configuration channel 1 of Port 1. Connect directly to the CC1 pin on the port's Type-C connector. Also connect a 390-pF capacitor to ground. |
| 38 | VBUS_C_1 | | Type-C connector BUS voltage of Port 1. Connect to the Type-C connector's VBUS pin. |
| 39 | VBUS_IN_1 | | Input of feedback voltage of error amplifier of Port 1. Connect to the VBUS node between the output current sense resistor and the VBUS provider NFET. |
| 40 | CSNO_1 | | Negative input of output CSA of Port 1. Connect to negative terminal of the output current sense resistor. |
| 41 | CSPO_1 | | Positive input of output CSA of Port 1. Connect to positive terminal of the output current sense resistor. |
| 42 | COMP_1 | | EA output pin of Port 1. Connect a compensation network to GND. Contact Infineon for assistance in designing the compensation network. |
| 43 | BST2_1 | | Boosted power supply of Port 1 boost high-side gate driver. Connect Schottky diode from VDDD to BST2_1. Bootstrap capacitor node. Also, connect a bootstrap capacitor from this pin to SW2_1. |
| 44 | HG2_1 | | Boost high-side gate driver output of Port 1. Connect to the boost (output) side sync (high side) FET gate. Use a wide trace to minimize inductance of this connection. |

Pin list

Table 2 EZ-PD™ CCG7D pinout table (continued)

| Pin# | Pin name | GPIO port assignment | Description |
|------|----------------|----------------------|---|
| 45 | SW2_1 | – | Negative power rail of Port 1 boost high-side gate driver. This is also connected to one input terminal of RCP of boost high-side gate driver. Connect to the switch node (inductor) on the boost (output) side. Use a short and wide trace to minimize the inductance and resistance of this connection. |
| 46 | VOUT_1 | | Output of the buck-boost converter of Port 1. This is also connected to one input terminal of RCP of boost high-side gate driver. Connect to the boost sync (high side) FET's drain. Use a dedicated (Kelvin) trace for this connection. |
| 47 | LG2_1 | | Boost low-side gate driver output of Port 1. Connect to the boost (output) side control (low side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 48 | PVDD_1 | | Supply of low-side gate driver of Port 1. Connect to VDDD. Use a 1 µF and 0.1 µF bypass capacitors as close to the EZ-PD™ CCG7D device as possible. |
| 49 | PGND_1 | | Ground of low-side gate driver of port 1. This is also connected to one input terminal of zero current detection of buck low-side gate driver. Connect directly to Port 0's board ground plane. |
| 50 | LG1_1 | | Buck low-side gate driver output of Port 1. Connect to the buck (input) side sync (low side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 51 | SW1_1 | | Negative power rail of Port 1 buck high-side gate driver. This is also connected to one input terminal of zero current detection of buck low-side gate driver. Connect to the switch node (inductor) on the buck (input) side. Use a short and wide trace to minimize the inductance and resistance of this connection. |
| 52 | HG1_1 | | Buck high-side gate driver output of Port 1. Connect to the buck (input) side control (high side) FET gate. Use a wide trace to minimize inductance of this connection. |
| 53 | BST1_1 | | Boosted power supply of Port 1 buck high-side gate driver. Connect Schottky diode from VDDD to BST1_1. Bootstrap capacitor node. |
| 54 | CSNI_1 | | Negative input of input CSA of Port 1. Connect to the negative terminal of the input current sense resistor. Use a dedicated (Kelvin) connection. |
| 55 | CSPI_1 | | Positive input of input CSA of Port 1. Connect to the positive terminal of the input current sense resistor. Use a dedicated (Kelvin) connection. |
| 56 | GPIO14/SWD_DAT | P3.0 | GPIO/SWD programming and debug data signal |
| 57 | GPIO15/SWD_CLK | P3.1 | GPIO/SWD programming and debug clock signal |
| 58 | GPIO16 | P3.2 | GPIO |
| 59 | GPIO17 | P3.3 | |
| 60 | GPIO18 | P3.4 | |
| 61 | VIN | – | 4 V–24 V Input supply. Connect a ceramic bypass capacitor to GND close to this pin. |
| 62 | VCCD | | 1.8-V core LDO output. Connect a 0.1-µF bypass capacitor to ground. Do not connect anything else to this pin. |
| 63 | VDDD | | 5-V LDO output. Connect to pin 25. Also connect a 10-µF bypass capacitor to this pin. |
| 64 | GND | | Chip ground. Connect to the EPAD and to pin 34. |
| 65 | CSPI_0 | | Positive input of input CSA of Port 0. Connect to the positive terminal of the input current sense resistor. Use a dedicated (Kelvin) connection. |
| 66 | CSNI_0 | | Negative input of input CSA of Port 0. Connect to the negative terminal of the input current sense resistor. Use a dedicated (Kelvin) connection. |
| 67 | BST1_0 | | Boosted power supply of Port 0 buck high-side gate driver. Bootstrap capacitor node. Connect Schottky diode from VDDD to BST1_0. Also, connect a bootstrap capacitor from this pin to SW1_0. |
| 68 | HG1_0 | | Buck high-side gate driver output of Port 0. Connect to the buck (input) side control (high side) FET gate. Use a wide trace to minimize inductance of this connection. |
| | EPAD | | Exposed ground pad. Connect directly to pins 34 and 64. |

Table 3 GPIO pins and functionality

| 68-QFN | | SCB function | | | Analog | TCPWM | | Fault protection |
|--------|--------------|-------------------|----------------------|------------------|-------------|-----------------|-----------------------------|----------------------|
| Pin | GPIO# | UART | SPI | I2C | | ACT #0 | ACT#1 | |
| 18 | CSN_0_GPIO0 | scb[1].uart_cts:0 | scb[1].spi_select0:0 | – | amuxbus_a/b | tcpwm.line[1]:0 | tcpwm.tr_compare_match[1]:0 | – |
| 19 | CSP_0_GPIO1 | scb[2].uart_rts:0 | scb[2].spi_miso:0 | – | amuxbus_a/b | tcpwm.line[0]:0 | tcpwm.tr_compare_match[0]:0 | – |
| 20 | GPIO2 | scb[2].uart_cts:0 | scb[2].spi_mosi:0 | – | amuxbus_a/b | – | – | usbpd[0].fault_gpio0 |
| 21 | GPIO3 | scb[2].uart_rx:0 | scb[2].spi_clk:0 | scb[2].i2c_scl:0 | amuxbus_a/b | tcpwm.line[0]:2 | – | – |
| 22 | GPIO4 | scb[2].uart_tx:0 | scb[2].spi_select0:0 | scb[2].i2c_sda:0 | amuxbus_a/b | tcpwm.line[1]:2 | – | – |
| 23 | DP_0_GPIO5 | scb[0].uart_cts:0 | scb[0].spi_mosi:0 | – | amuxbus_a/b | tcpwm.line[2]:2 | – | – |
| 24 | DM_0_GPIO6 | scb[0].uart_rts:0 | scb[0].spi_select0:0 | – | amuxbus_a/b | tcpwm.line[3]:2 | – | – |
| 26 | DM_1_GPIO7 | – | – | – | amuxbus_a/b | – | – | usbpd[1].fault_gpio1 |
| 27 | DP_1_GPIO8 | – | – | – | amuxbus_a/b | – | – | usbpd[0].fault_gpio1 |
| 29 | GPIO9 | scb[0].uart_tx:0 | scb[0].spi_miso:0 | scb[0].i2c_sda:0 | amuxbus_a/b | – | – | – |
| 30 | GPIO10 | scb[0].uart_rx:0 | scb[0].spi_clk:0 | scb[0].i2c_scl:0 | amuxbus_a/b | – | – | – |
| 31 | GPIO11 | scb[1].uart_tx:0 | scb[1].spi_mosi:0 | scb[1].i2c_sda:0 | amuxbus_a/b | tcpwm.line[2]:0 | – | usbpd[1].fault_gpio0 |
| 32 | CSP_1_GPIO12 | scb[1].uart_rx:0 | scb[1].spi_clk:0 | scb[1].i2c_scl:0 | amuxbus_a/b | tcpwm.line[3]:0 | tcpwm.tr_compare_match[3]:0 | – |
| 33 | CSN_1_GPIO13 | scb[1].uart_rts:0 | scb[1].spi_miso:0 | – | amuxbus_a/b | – | tcpwm.tr_compare_match[2]:0 | – |
| 56 | GPIO14 | scb[3].uart_tx:0 | scb[3].spi_miso:0 | scb[3].i2c_sda:0 | amuxbus_a/b | tcpwm.line[0]:1 | tcpwm.tr_compare_match[0]:1 | – |
| 57 | GPIO15 | scb[3].uart_rx:0 | scb[3].spi_clk:0 | scb[3].i2c_scl:0 | amuxbus_a/b | tcpwm.line[1]:1 | tcpwm.tr_compare_match[1]:1 | – |
| 58 | GPIO16 | scb[3].uart_cts:0 | scb[3].spi_mosi:0 | – | amuxbus_a/b | tcpwm.line[2]:1 | tcpwm.tr_compare_match[2]:1 | – |
| 59 | GPIO17 | scb[3].uart_rts:0 | scb[3].spi_select0:0 | – | amuxbus_a/b | tcpwm.line[3]:1 | tcpwm.tr_compare_match[3]:1 | – |
| 60 | GPIO18 | – | – | – | amuxbus_a/b | – | – | – |

Pin list

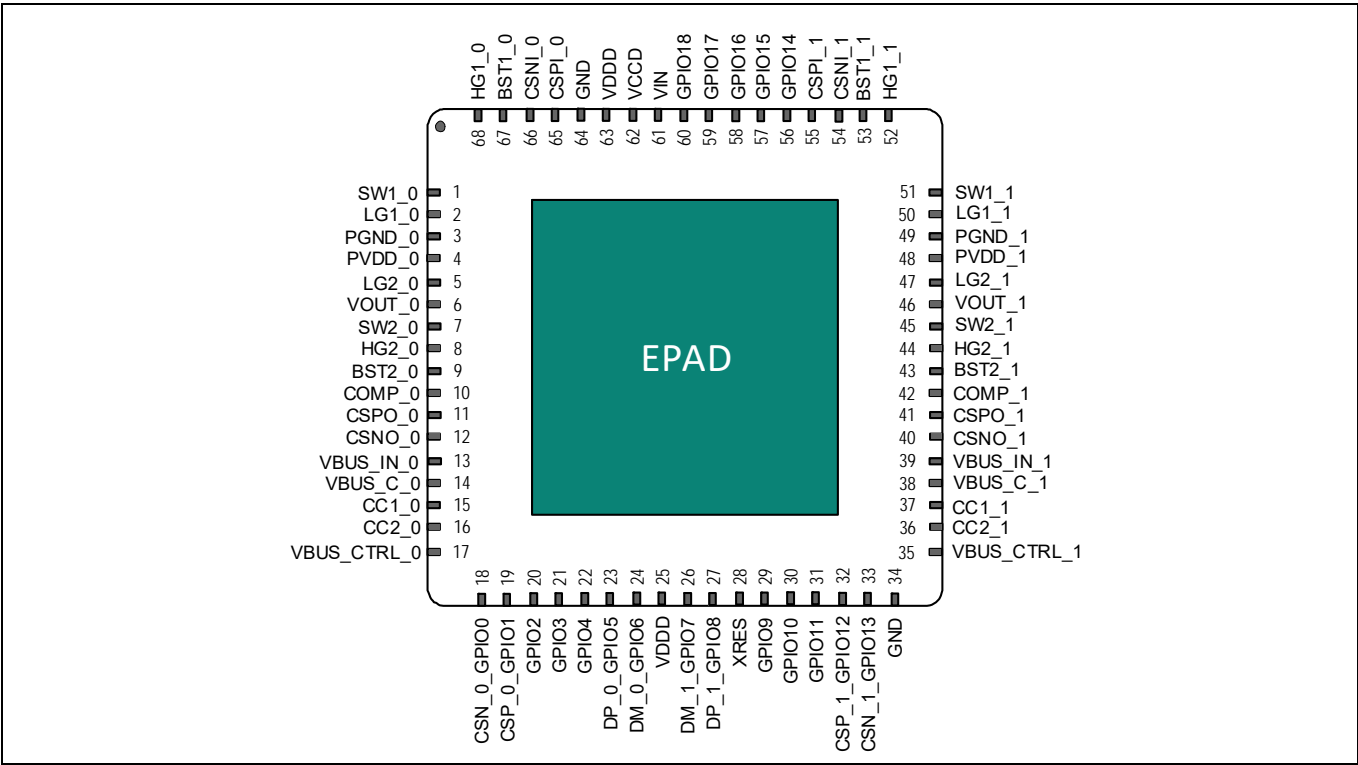


Figure 9 EZ-PD™ CCG7D 68-QFN pinout

4 EZ-PD™ CCG7D programming and bootloading

There are two ways to program application firmware into a CCG7D device:

1. Programming the device flash over SWD interface
2. Application firmware update over specific interfaces (CC, I2C)

Generally, the EZ-PD™ CCG7D devices are programmed over SWD interface only during development or during the manufacturing process of the end-product. Once the end-product is manufactured, the EZ-PD™ CCG7D device's application firmware can be updated via the appropriate bootloader interface. Infineon strongly recommends to use the **EZ-PD™ Configuration Utility** to turn off the application firmware update over CC or I2C interface in the firmware that is updated into EZ-PD™ CCG7D's flash before mass production. This prevents unauthorized firmware from being updated over CC interface in the field. If you desire to retain the application firmware update over CC/ I2C interfaces feature post-production for on-field firmware updates, contact **Infineon Sales** for further guidelines.

4.1 Programming the device flash over SWD interface

The EZ-PD™ CCG7D family of devices can be programmed using the SWD interface. Infineon provides programming kits (**CY8CKIT-002 MiniProg3 Kit**) called MiniProg3 and (**CY8CKIT-005 MiniProg4 Kit**) MiniProg4 which can be used to program the flash as well as debug firmware. The flash is programmed by downloading the information from a hex file. This hex file is a binary file generated as an output of building the firmware project in **PSOC™ Creator**. Click [here](#) for more information on how to use the MiniProg3 programmer. Click [here](#) for more information on how to use the MiniProg4 programmer. There are many third-party programmers that support mass programming in a manufacturing environment.

As shown in the block diagram in **Figure 10**, the SWD_DAT and SWD_CLK pins are connected to the host programmer's SWDIO (data) and SWDCLK (clock) pins respectively. During SWD programming, the device can be powered by the host programmer by connecting its VTARG (power supply to the target device) to VDDD pins of EZ-PD™ CCG7D device. If the EZ-PD™ CCG7D device is powered using an on-board power supply, it can be programmed using the "Reset Programming" option. For more details, see **CYPDXXXX Programming Specifications**.

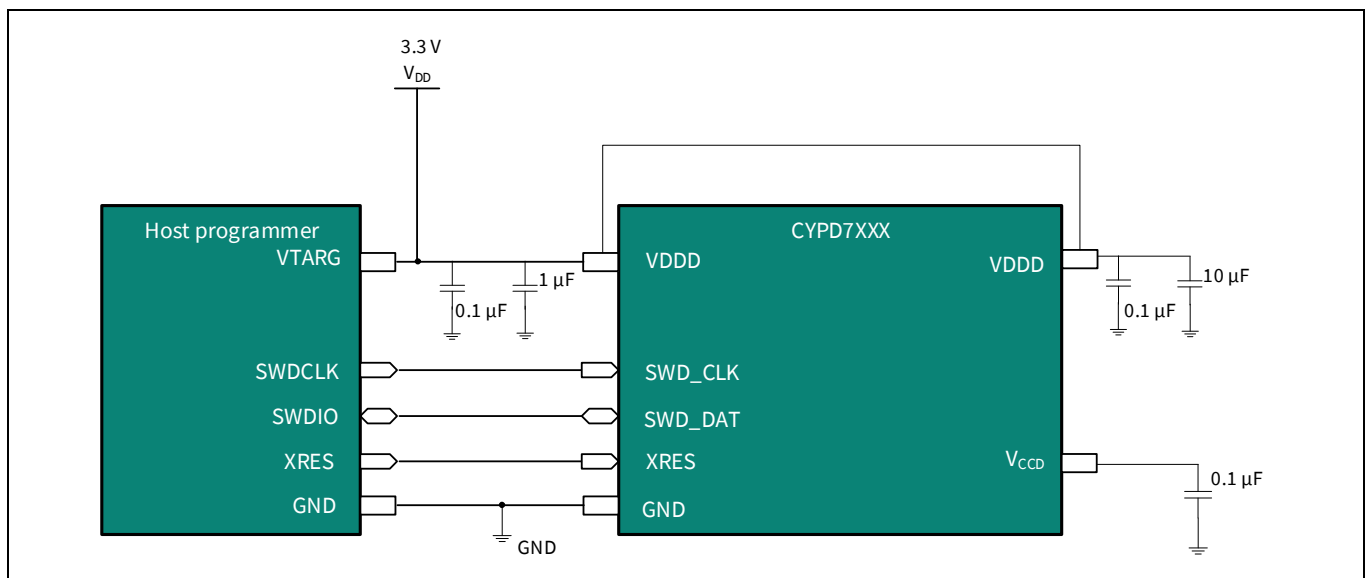


Figure 10 Connecting the programmer to CYPD7XXX device

4.2 Application firmware update using bootloader

There are two kinds of bootloader options available in EZ-PD™ CCG7D:

- CC and I2C bootloader – This bootloader has the GPIO 4, Pin 22 set to strong drive low to drive the FET for VBAT to GND short-circuit protection. VBUS_CTRL pin in the bootloader is configured to control the provider FET. The bootloader will work for designs with and without provider FET
- LIN bootloader – EZ-PD™ CCG7D parts will ship with the CC and I2C bootloader programmed at the factory

4.2.1 Application firmware update over CC interface

For bootloading EZ-PD™ CCG7D applications over the CC interface, the [CY4532 EVK](#) or [CCPROG PAT: USB-C Power Adapter Programmer and Tester](#) is used to send programming and configuration data as Infineon-specific vendor defined messages (VDMs) over the CC line. The CY4532 EVK's power board or PAT tester is connected to the system containing EZ-PD™ CCG7D device on one end and a Windows PC running the EZ-PD™ Configuration Utility as shown in [Figure 11](#) on the other end to boot load the EZ-PD™ CCG7D device.

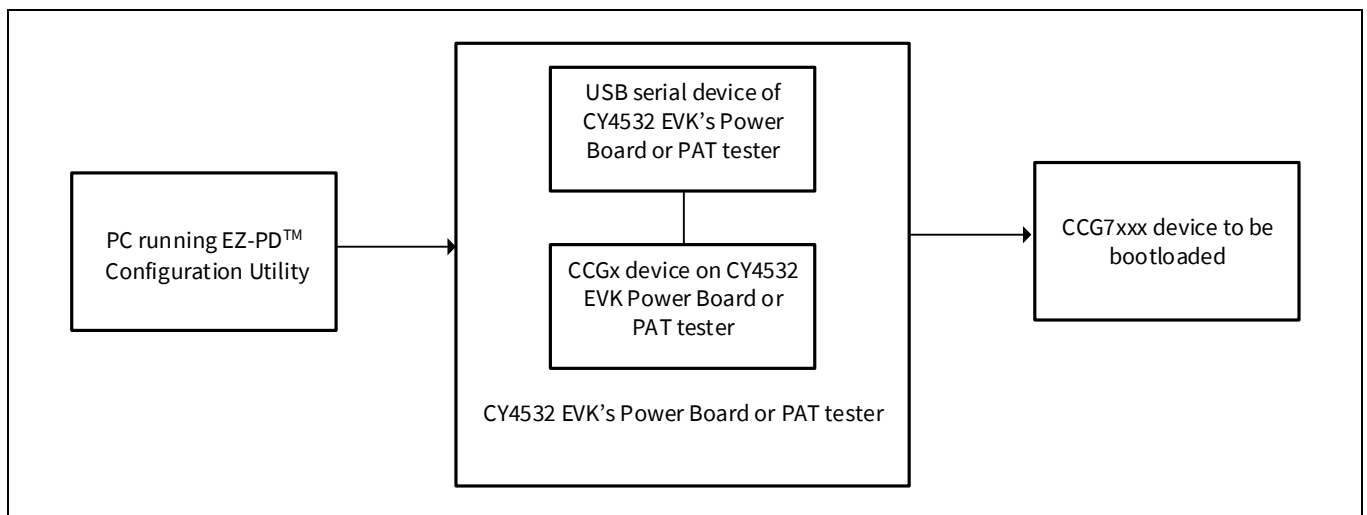


Figure 11 Application firmware update over CC interface

The application firmware (FW) update feature over CC interface is intended for use during development and manufacturing. Infineon strongly recommends customers to use the [EZ-PD™ Configuration Utility](#) to turn off the application FW update over CC interface in the firmware that is updated into EZ-PD™ CCG7D's flash before mass production. This prevents unauthorized firmware from being updated over CC-interface in the field. See the knowledge base article [KBA230192](#) on how to configure this in EZ-PD™ Configuration Utility. If you desire to retain the application firmware update over CC interface feature post-production for on-field firmware updates, contact [Infineon support](#) for further guidelines on how to use authenticated CC bootloader.

4.2.2 Application firmware update over I2C interface

The default bootloader supports both CC and I2C interface. For boot loading EZ-PD™ CCG7D applications over the I2C interface, any host processor can implement the legacy boot commands. Contact [Infineon support](#) for further details regarding the host processor implementation. The connections between the host processor and EZ-PD™ CCG7D for the bootloading via I2C interface is shown in [Figure 12](#).

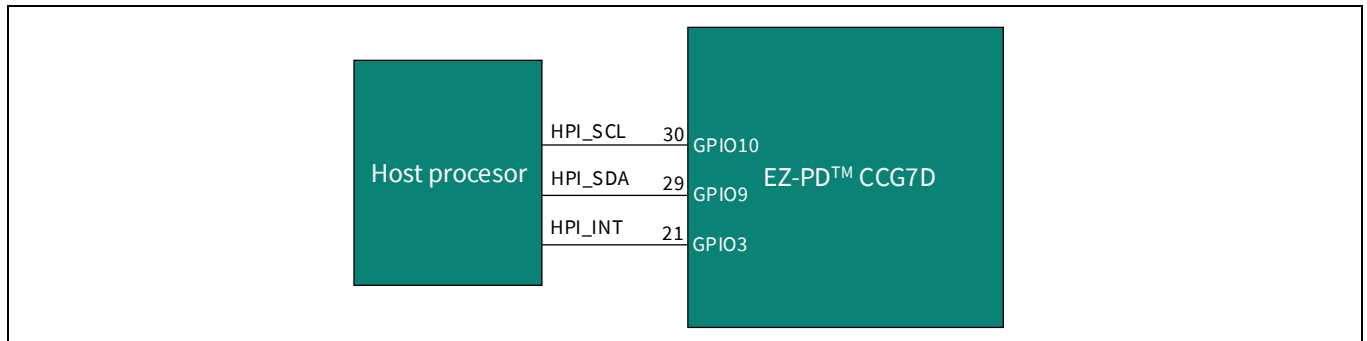


Figure 12 GPIO mapping for the application firmware update over I2C interface

4.2.3 Application firmware update over LIN interface

The LIN-based bootloader supports firmware and configuration updates over LIN interface using HPI. The Command sequence is same for all the bootloader interfaces irrespective of the underlying communication protocol (CC/I2C/LIN). The LIN bootloader will support standard diagnostic commands over UDS protocol thereby enabling easy integration with automotive LIN Network and helping in reduced design cycle time for customers. The default baud rate in the LIN bootloader is 19200. The connections between the LIN transceiver and EZ-PD™ CCG7D for the bootloading via LIN interface is shown in [Figure 13](#).

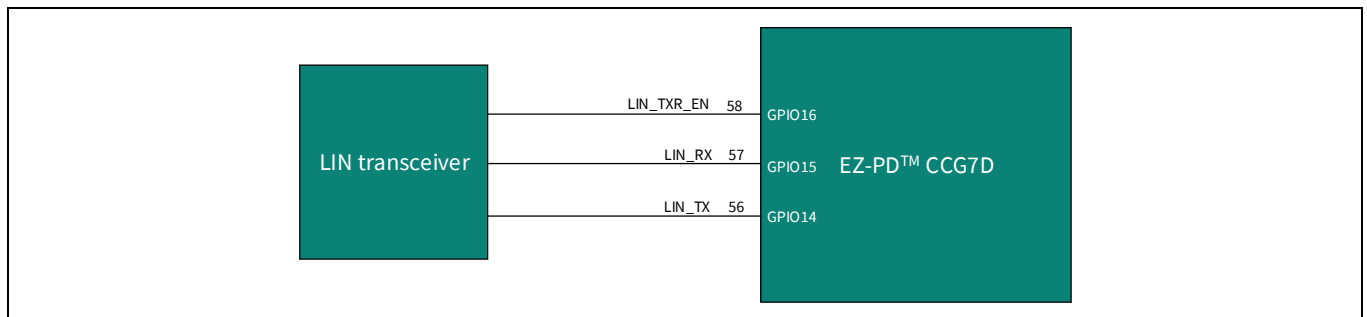


Figure 13 GPIO mapping for the application firmware update over LIN interface

5 Applications

Figure 14 shows a typical head unit charger application block diagram using EZ-PD™ CCG7D. A head unit charger (also known as center stack) is located prominently in the center of the dashboard or console. They are powered by the car battery and are used for charging the mobile/tablet and for media transfer using USB data communications. In this application, EZ-PD™ CCG7D will always be in DFP role supporting the charging of the device. It negotiates the power with the connected device and uses the integrated buck-boost controller to supply the required voltage and current.

The DP/DM lines of the Type-C receptacles are connected to the host processor/hub, for data connectivity to the head unit (HU). These pins are also connected to EZ-PD™ CCG7D to support legacy charging protocol BC v1.2 CDP. The I²C interface is used to interface with the host processor/hub, to support host processor interface (HPI) commands, provide status to the Head Unit, and support FW updates. Note that per the Battery Charging Specification 1.2, other legacy charging protocols other than BC v1.2 CDP cannot be supported in conjunction with USB data communication.

EZ-PD™ CCG7D measures various temperatures using external NTC thermistors. EZ-PD™ CCG7D throttles the output power based on temperature and/or shuts off the power under critical conditions. It also monitors the battery voltage and lowers the output power if the battery voltage is lower than the user-configured threshold. When no load is connected to the USB Type-C port, EZ-PD™ CCG7D remains in standby mode without switching on the buck-boost controller.

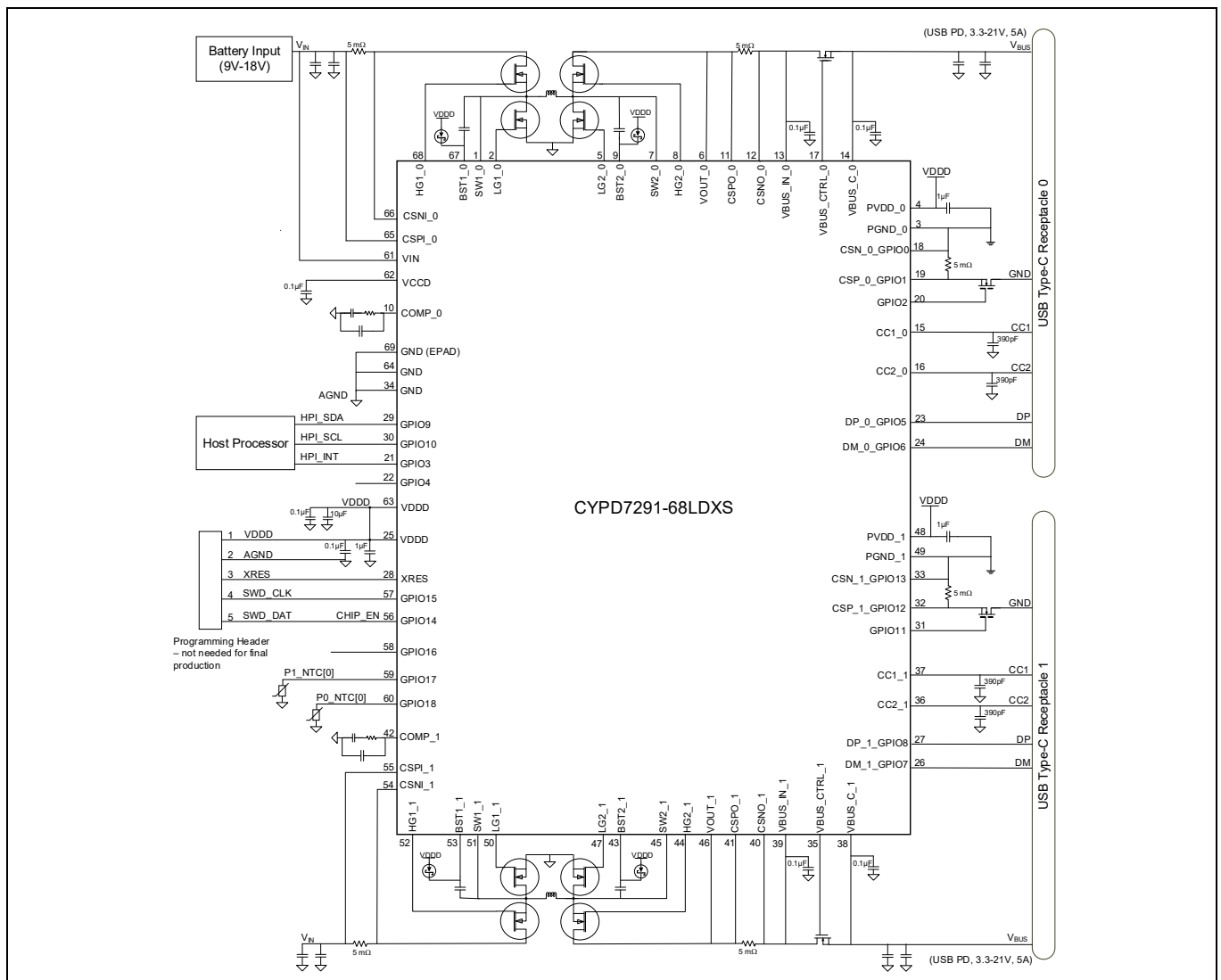


Figure 14 EZ-PD™ CCG7D head unit charger application diagram

Table 4 Head unit (HU) GPIO pin mapping for application diagram in [Figure 14](#)

| Pin # | Pin name | Function | GPIO | HU |
|-------|--------------|--|------|-------------|
| 18 | CSN_0_GPIO0 | Port 0: CSN pin on ground side to implement VBAT to GND short circuit protection | P0.0 | P0_VBAT_CSN |
| 19 | CSP_0_GPIO1 | Port 0: CSP pin on ground side to implement VBAT to GND short circuit protection | P0.1 | P0_VBAT_CSP |
| 20 | GPIO2 | Port 0: GPIO to disable the FET for VBAT to GND short circuit protection | P0.2 | P0_VBAT_FET |
| 21 | GPIO3 | HPI Interrupt | P0.3 | HPI_INT |
| 22 | GPIO4 | GPIO, available for system level function | P0.4 | GPIO |
| 23 | DP_0_GPIO5 | Port 0: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.0 | P0_DP |
| 24 | DM_0_GPIO6 | Port 0: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.1 | P0_DM |
| 26 | DM_1_GPIO7 | Port 1: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.2 | P1_DM |
| 27 | DP_1_GPIO8 | Port 1: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.3 | P1_DP |
| 29 | GPIO9 | HPI data (SDA) | P2.0 | HPI_SDA |
| 30 | GPIO10 | HPI clock (SCL) | P2.1 | HPI_SCL |
| 31 | GPIO11 | Port 1: GPIO to disable the FET for VBAT to GND short circuit protection | P1.4 | P1_VBAT_FET |
| 32 | CSP_1_GPIO12 | Port 1: CSP pin on ground side to implement VBAT to GND short circuit protection | P1.5 | P1_VBAT_CSP |
| 33 | CSN_1_GPIO13 | Port 1: CSN pin on ground side to implement VBAT to GND short circuit protection | P1.6 | P1_VBAT_CSN |
| 56 | GPIO14 | Connect to the host programmer's SWDIO (data) for programming the EZ-PD™ CCG7D device | P3.0 | GPIO |
| 57 | GPIO15 | Connect to the host programmer's SWDCLK (clock) for programming the EZ-PD™ CCG7D Chip Enable pin | P3.1 | CHIP_EN |
| 58 | GPIO16 | GPIO, available for system level function | P3.2 | GPIO |
| 59 | GPIO17 | Port 1: Thermistor | P3.3 | P1_NTC[0] |
| 60 | GPIO18 | Port 0: Thermistor | P3.4 | P0_NTC[0] |

EZ-PD™ CCG7D Automotive USB dual-port Type-C with PD and buck-boost controller



Applications

Figure 15 shows a typical rear seat charger application block diagram using EZ-PD™ CCG7D. This application is similar to the head unit charger application without the hub and data communications. There is no host processor/hub in this application. This application can be configured to support the legacy charging protocols – BC1.2 DCP, Qualcomm QC2.0/3.0, Apple charging, and Samsung AFC.

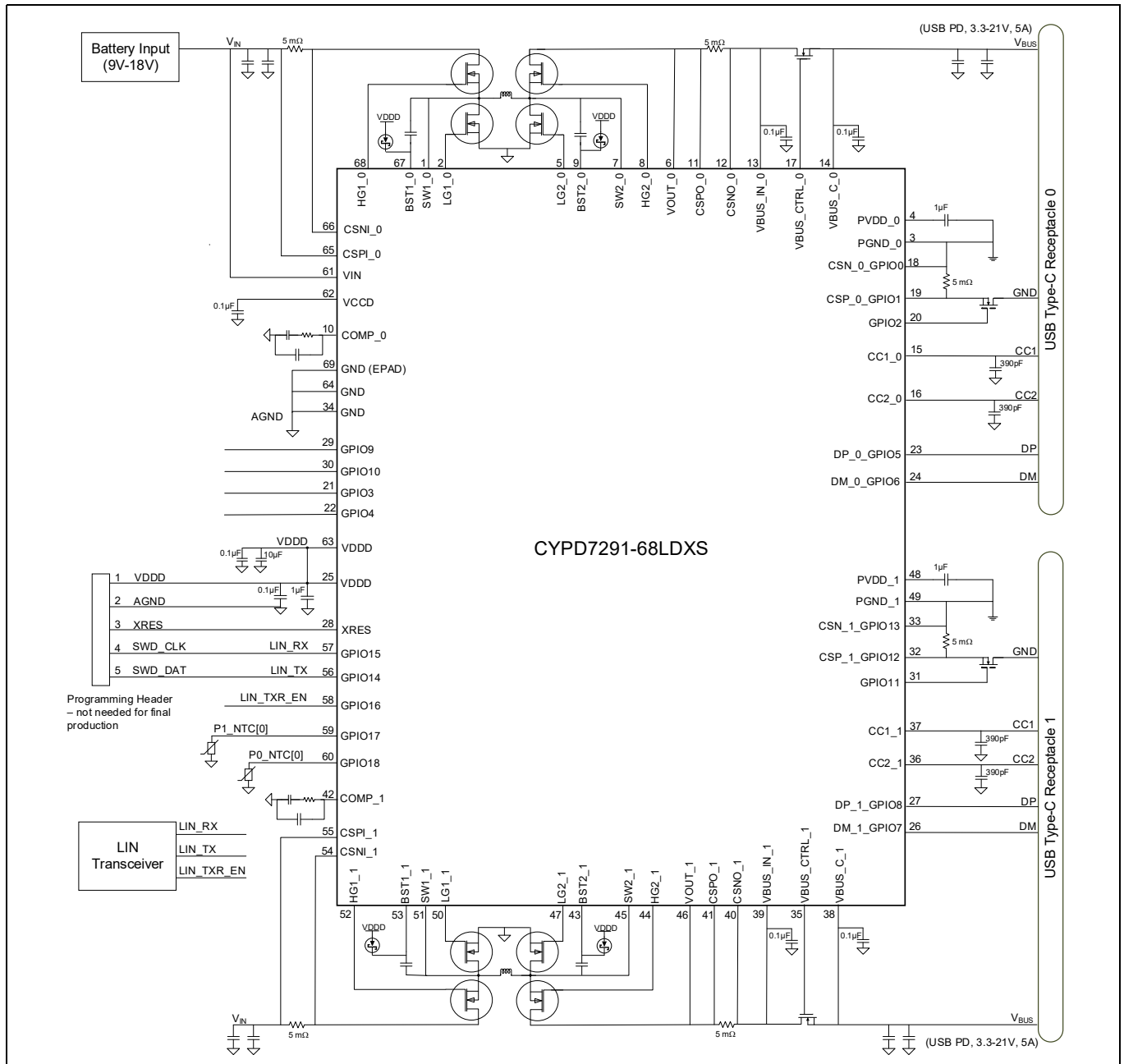


Figure 15 EZ-PD™ CCG7D RSC application diagram

Table 5 RSC GPIO pin mapping for application diagram in Figure 15

| Pin # | Pin name | Function | GPIO | RSC |
|-------|--------------|---|------|-------------|
| 18 | CSN_0_GPIO0 | Port 0: CSN pin on ground side to implement VBAT to GND short circuit protection | P0.0 | P0_VBAT_CSN |
| 19 | CSP_0_GPIO1 | Port 0: CSP pin on ground side to implement VBAT to GND short circuit protection | P0.1 | P0_VBAT_CSP |
| 20 | GPIO2 | Port 0: GPIO to disable the FET for VBAT to GND short circuit protection | P0.2 | P0_VBAT_FET |
| 21 | GPIO3 | GPIO, available for system level function | P0.3 | GPIO |
| 22 | GPIO4 | GPIO, available for system level function | P0.4 | GPIO |
| 23 | DP_0_GPIO5 | Port 0: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.0 | P0_DP |
| 24 | DM_0_GPIO6 | Port 0: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.1 | P0_DM |
| 26 | DM_1_GPIO7 | Port 1: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.2 | P1_DM |
| 27 | DP_1_GPIO8 | Port 1: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.3 | P1_DP |
| 29 | GPIO9 | GPIO, available for system level function | P2.0 | GPIO |
| 30 | GPIO10 | GPIO, available for system level function | P2.1 | GPIO |
| 31 | GPIO11 | Port 1: GPIO to disable the FET for VBAT to GND short circuit protection | P1.4 | P1_VBAT_FET |
| 32 | CSP_1_GPIO12 | Port 1: CSP pin on ground side to implement VBAT to GND short circuit protection | P1.5 | P1_VBAT_CSP |
| 33 | CSN_1_GPIO13 | Port 1: CSN pin on ground side to implement VBAT to GND short circuit protection | P1.6 | P1_VBAT_CSN |
| 56 | GPIO14 | LIN TX pin Connect to the host programmer's SWDIO (data) for programming the EZ-PD™ CCG7D device | P3.0 | LIN_TX |
| 57 | GPIO15 | LIN RX pin Connect to the host programmer's SWDCLK (clock) for programming the EZ-PD™ CCG7D | P3.1 | LIN_RX |
| 58 | GPIO16 | LIN Transceiver enable | P3.2 | LIN_TXR_EN |
| 59 | GPIO17 | Port 1: Thermistor | P3.3 | P1_NTC[0] |
| 60 | GPIO18 | Port 0: Thermistor | P3.4 | P0_NTC[0] |

Applications

Figure 16 shows the rear seat entertainment (RSE) application block diagram using EZ-PD™ CCG7D. In the RSE application, one port is a dedicated charge-only port and the second port is used for charging and streaming video content to the rear-seat monitor, using a mobile phone, PC, or a tablet. The implementation of the charging-only port is identical to the RSC application. EZ-PD™ CCG7D supports display port alternate mode sink in the port that supports video streaming and controls the external display port multiplexer over I²C. EZ-PD™ CCG7D also communicates with the system's SoC over I²C.

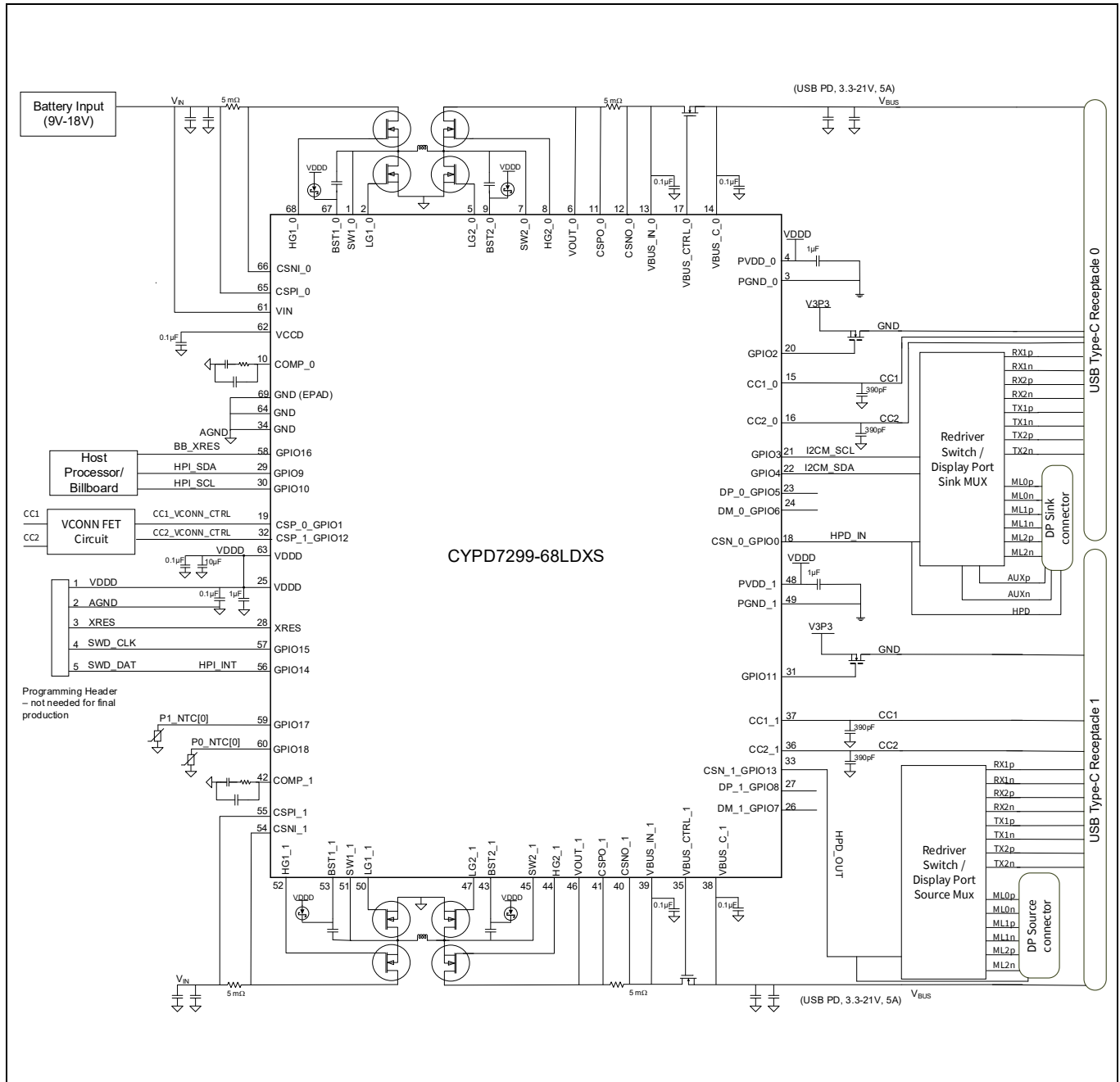


Figure 16 **EZ-PD™ CCG7D RSE application diagram**

Table 6 RSE GPIO pin mapping for application diagram in Figure 16

Port 0: Display and charger port

Port 1: Charge only port

| Pin # | Pin name | Function | GPIO | RSE |
|-------|--------------|--|------|------------------------|
| 18 | CSN_0_GPIO0 | Display port sink MUX Hot Plug Detect | P0.0 | HPD_IN |
| 19 | CSP_0_GPIO1 | CC1 Vconn control | P0.1 | CC1_VCONN_CTRL |
| 20 | GPIO2 | Port 0: GPIO to disable the FET for VBAT to GND short circuit protection | P0.2 | P0_VBAT_FET |
| 21 | GPIO3 | I ² C Master Clock (SCL) for controlling the Display port Mux | P0.3 | I2CM_SCL |
| 22 | GPIO4 | I ² C Master Data (SDA) for controlling the Display port Mux | P0.4 | I2CM_SDA |
| 23 | DP_0_GPIO5 | GPIO, available for system level function | P1.0 | GPIO |
| 24 | DM_0_GPIO6 | GPIO, available for system level function | P1.1 | GPIO |
| 26 | DM_1_GPIO7 | Port 1: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.2 | P1_DM |
| 27 | DP_1_GPIO8 | Port 1: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.3 | P1_DP |
| 29 | GPIO9 | HPI data (SDA) | P2.0 | HPI_SDA [BILLBOARD] |
| 30 | GPIO10 | HPI clock (SCL) | P2.1 | HPI_SCL [BILLBOARD] |
| 31 | GPIO11 | Port 1: GPIO to disable the FET for VBAT to GND short circuit protection | P1.4 | P1_VBAT_FET |
| 32 | CSP_1_GPIO12 | Port 1: CSP pin on ground side to implement VBAT to GND short circuit protection | P1.5 | P1_VBAT_CSP |
| 33 | CSN_1_GPIO13 | Display Port Source MUX HPI OUT | P1.6 | HPI_OUT |
| 56 | GPIO14 | HPI interrupt / SWD Data | P3.0 | HPI_INT/SWD_DAT |
| 57 | GPIO15 | SWD clock | P3.1 | SWD_CLK |
| 58 | GPIO16 | BillBoard XRES | P3.2 | BB_XRES |
| 59 | GPIO17 | Port 1: Thermistor | P3.3 | P1_NTC[0] |
| 60 | GPIO18 | Port 0: Thermistor | P3.4 | P0_NTC[0] |

Figure 17 shows a RSC buck application block diagram using EZ-PD™ CCG7D. This application uses the integrated buck controller to supply the required voltage and current to the connected device. This application is identical to the Rear Seat Charger application, except that this application uses only buck topology when compared to the buck-boost topology in the standard RSC application. In a buck application, the negotiated voltage should always be lower than the input voltage. If the input voltage drops lower than the output voltage, then the output voltage will not be maintained and the port will shut down. This application can also be configured to support the legacy charging protocols – BC1.2 DCP, Qualcomm QC2.0/3.0, Apple charging, and Samsung AFC.

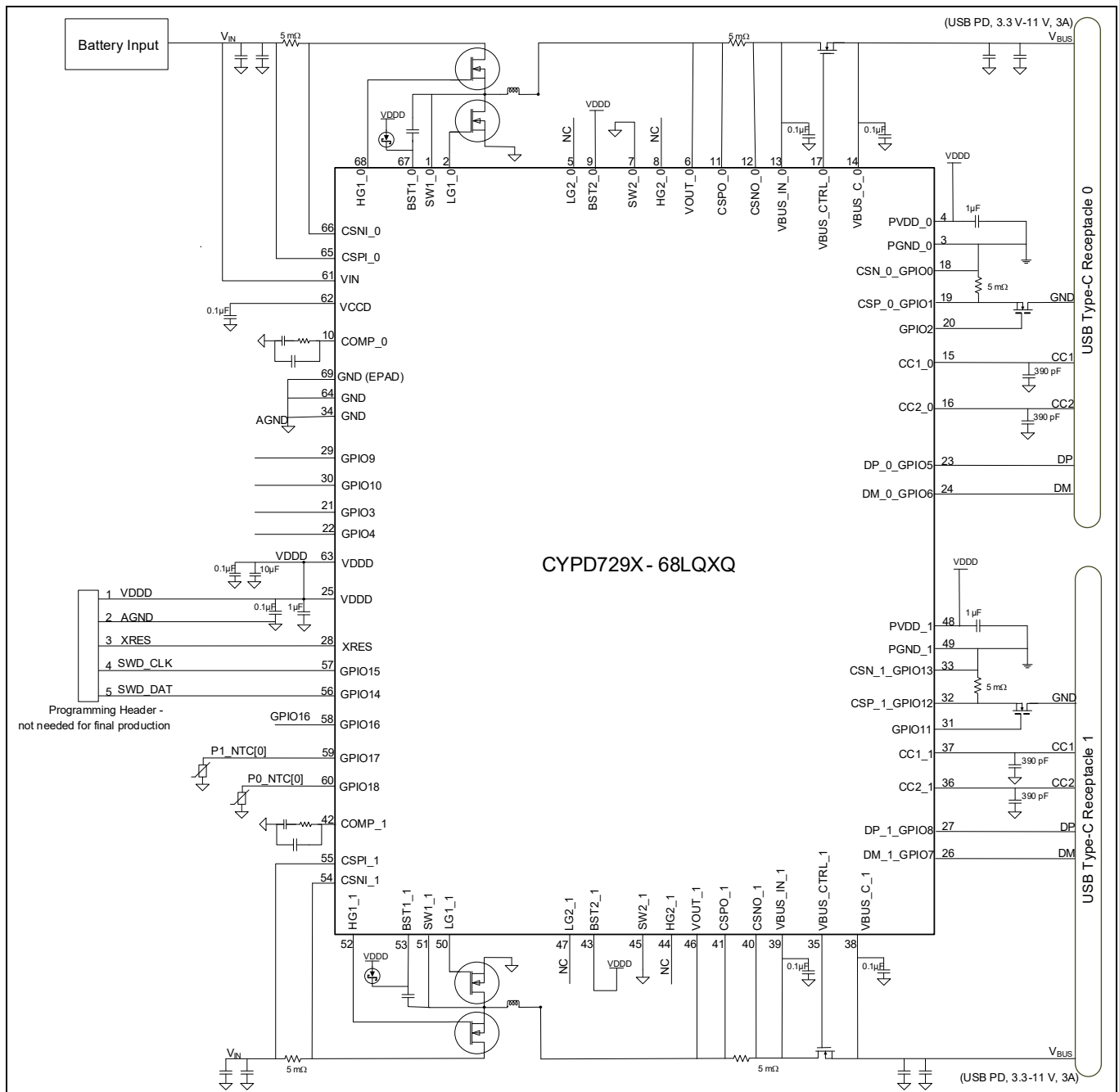


Figure 17 EZ-PD™ CCG7D RSC buck application diagram

Table 7 RSC buck GPIO pin mapping for application diagram in [Figure 17](#)

| Pin # | Pin name | Function | GPIO | RSC |
|-------|--------------|---|------|-------------|
| 18 | CSN_0_GPIO0 | Port 0: CSN pin on ground side to implement VBAT to GND short circuit protection | P0.0 | P0_VBAT_CSN |
| 19 | CSP_0_GPIO1 | Port 0: CSP pin on ground side to implement VBAT to GND short circuit protection | P0.1 | P0_VBAT_CSP |
| 20 | GPIO2 | Port 0: GPIO to disable the FET for VBAT to GND short circuit protection | P0.2 | P0_VBAT_FET |
| 21 | GPIO3 | GPIO, available for system level function | P0.3 | GPIO |
| 22 | GPIO4 | GPIO, available for system level function | P0.4 | GPIO |
| 23 | DP_0_GPIO5 | Port 0: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.0 | P0_DP |
| 24 | DM_0_GPIO6 | Port 0: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.1 | P0_DM |
| 26 | DM_1_GPIO7 | Port 1: USB DM of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.2 | P1_DM |
| 27 | DP_1_GPIO8 | Port 1: USB DP of Type-C port. Supports BC 1.2, QC, Apple Charging and AFC | P1.3 | P1_DP |
| 29 | GPIO9 | GPIO, available for system level function | P2.0 | GPIO |
| 30 | GPIO10 | GPIO, available for system level function | P2.1 | GPIO |
| 31 | GPIO11 | Port 1: GPIO to disable the FET for VBAT to GND short circuit protection | P1.4 | P1_VBAT_FET |
| 32 | CSP_1_GPIO12 | Port 1: CSP pin on ground side to implement VBAT to GND short circuit protection | P1.5 | P1_VBAT_CSP |
| 33 | CSN_1_GPIO13 | Port 1: CSN pin on ground side to implement VBAT to GND short circuit protection | P1.6 | P1_VBAT_CSN |
| 56 | GPIO14 | Connect to the host programmer's SWDIO (data) for programming the EZ-PD™ CCG7D device | P3.0 | SWDIO |
| 57 | GPIO15 | Connect to the host programmer's SWDCLK (clock) for programming the EZ-PD™ CCG7D | P3.1 | SWDCLK |
| 58 | GPIO16 | GPIO, available for system-level function | P3.2 | GPIO |
| 59 | GPIO17 | Port 1: Thermistor | P3.3 | P1_NTC[0] |
| 60 | GPIO18 | Port 0: Thermistor | P3.4 | P0_NTC[0] |

6 Electrical specifications

6.1 Absolute maximum ratings

Table 8 Absolute maximum ratings^[1]

| Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------------------------|--|------|-----|------------------------|------|--|
| V _{IN_MAX} | Maximum input supply voltage | – | – | 40 | V | – |
| V _{DDD_MAX} | Maximum supply voltage relative to V _{SS} | | | 6 | | |
| V _{5V_MAX} | Maximum supply voltage relative to V _{SS} | | | | | |
| V _{BUS_C_MAX} | Max V _{BUS_C} (P0/P1) voltage relative to V _{SS} | | | 24 | | |
| V _{CC_PIN_ABS} | Max voltage on CC1 and CC2 pins | | | | | |
| V _{GPIO_ABS} | Inputs to GPIO | –0.5 | | V _{DDD} + 0.5 | | |
| V _{GPIO_OVT_ABS} | OVT GPIO voltage | | | 6 | | |
| I _{GPIO_ABS} | Maximum current per GPIO | –25 | | 25 | mA | Absolute max, current injected per pin |
| I _{GPIO_INJECTION} | GPIO injection current, Max for V _{IH} > V _{DDD} , and Min for V _{IL} < V _{SS} | –0.5 | | 0.5 | | |
| ESD_HBM | Electrostatic discharge human body model | 2000 | | – | V | All pins. |
| ESD_CDM | Electrostatic discharge (ESD) charged device model | 500 | | | | Charged device model ESD |
| LU | Pin current for latch-up | –100 | | 100 | mA | – |
| T _J | Junction temperature | –40 | | 125 | °C | |

Note

- Usage above the absolute maximum conditions listed in **Table 8** may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 9 Pin based absolute maximum ratings

| Pin # | Pin name | Absolute minimum (V) | Absolute maximum (V) |
|-------|-----------------------------------|----------------------|----------------------|
| 1 | SW1_0 | -0.7 | 35 |
| 2 | LG1_0 ^[2] | -0.5 | PVDD + 0.5 |
| 3 | PGND_0 | -0.3 | 0.3 |
| 4 | PVDD_0 | - | VDDD |
| 5 | LG2_0 ^[2] | -0.5 | PVDD + 0.5 |
| 6 | VOUT_0 | -0.3 | 24 |
| 7 | SW2_0 | | |
| 8 | HG2_0 (wrt SW2_0) ^[2] | -0.5 | PVDD + 0.5 |
| 9 | BST2_0 (wrt SW2_0) ^[2] | - | PVDD + 0.5 |
| 10 | COMP_0 ^[2] | -0.5 | PVDD + 0.5 |
| 11 | CSPO_0 | -0.3 | 24 |
| 12 | CSNO_0 | | |
| 13 | VBUS_IN_0 | | |
| 14 | VBUS_C_0 | | |
| 15 | CC1_0 | -0.5 | |
| 16 | CC2_0 | | |
| 17 | VBUS_CTRL_0 | | 32 |
| 18 | CSN_0_GPIO0 ^[2] | | PVDD + 0.5 |
| 19 | CSP_0_GPIO1 ^[2] | | |
| 20 | GPIO2 ^[2] | | |
| 21 | GPIO3 ^[2] | | |
| 22 | GPIO4 ^[2] | | |
| 23 | DP_0_GPIO5 ^[2] | | |
| 24 | DM_0_GPIO6 ^[2] | | |
| 25 | VDDD | - | 6 |
| 26 | DM_1_GPIO7 ^[2] | -0.5 | PVDD + 0.5 |
| 27 | DP_1_GPIO8 ^[2] | | |
| 28 | XRES ^[2] | | |
| 29 | GPIO9 ^[2] | | |
| 30 | GPIO10 ^[2] | | |
| 31 | GPIO11 ^[2] | | |
| 32 | CSP_1_GPIO12 ^[2] | | |
| 33 | CSN_1_GPIO13 ^[2] | | |
| 34 | GND | - | - |

Note

2. Max voltage cannot exceed 6 V.
3. Max absolute voltage w.r.t. GND must not exceed 40 V.

Electrical specifications

Table 9 Pin based absolute maximum ratings (continued)

| Pin # | Pin name | Absolute minimum (V) | Absolute maximum (V) |
|-------|--------------------------------------|----------------------|----------------------|
| 35 | VBUS_CTRL_1 | −0.5 | 32 |
| 36 | CC2_1 | | 24 |
| 37 | CC1_1 | | |
| 38 | VBUS_C_1 | −0.3 | |
| 39 | VBUS_IN_1 | | |
| 40 | CSNO_1 | | |
| 41 | CSPO_1 | −0.3 | 24 |
| 42 | COMP_1 ^[1] | −0.5 | PVDD + 0.5 |
| 43 | BST2_1 ^[1] (wrt SW2_1) | − | |
| 44 | HG2_1 ^[1] (wrt SW2_1) | −0.5 | |
| 45 | SW2_1 | −0.3 | 24 |
| 46 | VOUT_1 | | |
| 47 | LG2_1 ^[1] | −0.5 | PVDD + 0.5 |
| 48 | PVDD_1 | − | VDDD |
| 49 | PGND_1 | −0.3 | 0.3 |
| 50 | LG1_1 ^[1] | −0.5 | PVDD + 0.5 |
| 51 | SW1_1 | −0.7 | 35 |
| 52 | HG1_1 ^[1, 2] (wrt SW1_1) | −0.5 | PVDD + 0.5 |
| 53 | BST1_1 ^[1, 2] (wrt SW1_1) | − | |
| 54 | CSNI_1 | −0.3 | 40 |
| 55 | CSPI_1 | | |
| 56 | GPIO14/SWD_DAT ^[1] | −0.5 | PVDD + 0.5 |
| 57 | GPIO15/SWD_CLK ^[1] | | |
| 58 | GPIO16 ^[1] | | |
| 59 | GPIO17 ^[1] | | |
| 60 | GPIO18 ^[1] | | |
| 61 | VIN | −0.3 | 40 |
| 62 | VCCD | − | − |
| 63 | VDDD | | 6 |
| 64 | GND | | − |
| 65 | CSPI_0 | −0.3 | 40 |
| 66 | CSNI_0 | | |
| 67 | BST1_0 ^[1, 2] (wrt SW1_0) | − | PVDD + 0.5 |
| 68 | HG1_0 ^[1, 2] (wrt SW1_0) | −0.5 | |
| | EPAD | − | − |

Note

2. Max voltage cannot exceed 6 V.
3. Max absolute voltage w.r.t. GND must not exceed 40 V.

Electrical specifications

6.2 Device-level specifications

All specifications are valid for $-40^{\circ}\text{C} \leq T_A \leq 105^{\circ}\text{C}$ and $T_J \leq 125^{\circ}\text{C}$, except where noted. Specifications are valid for 3.0 V to 5.5 V except where noted.

6.2.1 DC specifications

Table 10 DC specifications (operating conditions)

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|-----------------------|---|-----------------------|-----|------|------|---|
| SID.PWR#1 | V _{IN} | Input supply voltage | 4.0 | – | 24 | V | – |
| SID.PWR#1A | V _{IN_BB} | Buck boost operating input supply voltage | 5.5 | | 24 | | |
| SID.PWR#2 | V _{DDD_REG} | V _{DDD} output with V _{IN} 5.5 to 24 V, Max load = 150 mA | 4.6 | | 5.5 | | |
| SID.PWR#3 | V _{DDD_MIN} | V _{DDD} output with V _{IN} 4 to 5.5 V, Max load = 20 mA | V _{IN} – 0.2 | | – | | |
| SID.PWR#20 | VBUS | VBUS_C_0/1 valid range | 3.3 | | 21.5 | | |
| SID.PWR#5 | V _{CCD} | Regulated output voltage (for Core Logic) | – | 1.8 | – | | |
| SID.PWR#16 | C _{EFC_VCCD} | External regulator voltage bypass for VCCD | 80 | 100 | 120 | nF | X5R ceramic |
| SID.PWR#17 | C _{EXC_VDDD} | Power supply decoupling capacitor for V _{DDD} | – | 10 | – | μF | |
| SID.PWR#18 | C _{EXV} | Bootstrap supply capacitor (BST1_0, BST1_1, BST2_0, BST2_1) | | 0.1 | | | |
| SID.PWR#24 | I _{DD_ACT} | Supply current at 0.4 MHz switching frequency | | 85 | | mA | T _A = 25°C, V _{IN} = 12 V. CC IO IN Transmit or Receive, no I/O sourcing current, No VCONN load current, CPU at 24 MHz, two PD ports active. Buck-boost converter ON, 3-nF gate driver capacitance. |

Deep Sleep mode

| | | | | | | | |
|---------|---------------|--|---|-----|---|---------------|---|
| SID_DS1 | I_{DD_DS1} | $V_{IN} = 12\text{ V}$. CC wakeup on, Type-C not connected. | – | 110 | – | μA | Type-C not attached, CC enabled for wakeup. Rp connection should be enabled for both PD ports. $T_A = 25^{\circ}\text{C}$. All faults disabled including VBAT-GND. |
| SID_DS2 | I_{DD_DS2} | $V_{IN} = 12\text{ V}$ | – | 50 | – | μA | USB PD disabled. Wake-up from GPIO. $T_A = 25^{\circ}\text{C}$. |
| SID_DS3 | I_{DD_DS3} | $V_{IN} = 12\text{ V}$. CC wakeup on, Type-C not connected. | | 450 | | | Type-C not attached, CC enabled for wakeup. Rp connection should be enabled for both PD ports. $T_A = 25^{\circ}\text{C}$. All faults disabled except VBAT-GND. |

Electrical specifications

6.2.2 CPU

Table 11 CPU specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|------------------------|---|-----|-----|-----|------|--|
| SID.CLK#4 | F _{CPU} | CPU input frequency | – | – | 48 | MHz | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID.PWR#19 | T _{DEEPSLEEP} | Wakeup from Deep Sleep mode | – | 35 | – | μs | – |
| SYS.XRES#5 | T _{XRES} | External reset pulse width | 5 | – | – | – | – |
| SYS.FES#1 | T _{PWR_RDY} | Power-up to “Ready to accept I ² C/CC command” | – | 5 | 25 | ms | – |

6.2.3 GPIO

Table 12 GPIO DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|----------------------|---|------------------------|-----|------------------------|------|---|
| SID.GIO#9 | V _{IH_CMOS} | Input voltage HIGH threshold | 0.7 × V _{DDD} | – | – | V | CMOS input |
| SID.GIO#10 | V _{IL_CMOS} | Input voltage LOW threshold | – | – | 0.3 × V _{DDD} | – | – |
| SID.GIO#7 | V _{OH_3V} | Output voltage HIGH level | V _{DDD} – 0.6 | – | – | – | I _{OH} = –4 mA, –40°C ≤ T _A ≤ +105°C |
| SID.GIO#8 | V _{OL_3V} | Output voltage LOW level | – | – | 0.6 | – | I _{OL} = 10 mA, –40°C ≤ T _A ≤ +105°C |
| SID.GIO#2 | R _{pu} | Pull-up resistor when enabled | 3.5 | 5.6 | 8.5 | kΩ | –40°C ≤ T _A ≤ +105°C |
| SID.GIO#3 | R _{pd} | Pull-down resistor when enabled | – | – | – | – | – |
| SID.GIO#4 | I _{IL} | Input leakage current (absolute value) | – | – | 2 | nA | +25°C T _A , 3-V V _{DDD} |
| SID.GIO#5 | C _{PIN_A} | Max pin capacitance | – | – | 22 | pF | –40°C ≤ T _A ≤ +105°C, Capacitance on DP, DM pins |
| SID.GIO#6 | C _{PIN} | Max pin capacitance | – | 3 | 7 | pF | –40°C ≤ T _A ≤ +105°C, ALL V _{DDD} , All other I/Os |
| SID.GIO#11 | V _{IHTTL} | LVTTL input | 2 | – | – | V | –40°C ≤ T _A ≤ +105°C |
| SID.GIO#12 | V _{ILTTL} | LVTTL input | – | – | 0.8 | – | – |
| SID.GIO#13 | V _{HYSTTL} | Input hysteresis, LVTTL, V _{DDD} > 2.7 V | 100 | – | – | mV | V _{DDD} > 2.7 V |
| SID.GIO#14 | V _{HYSCMOS} | Input hysteresis CMOS | 0.1 × V _{DDD} | – | – | – | – |

Electrical specifications

Table 13 GPIO AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions | |
|------------|------------------------|--|-----|-----|-----|------|---|---------------------------------|
| SID.GIO#16 | T _{RISEF} | Rise time in Fast Strong mode | 2 | – | 12 | ns | C _{load} = 25 pF, –40°C ≤ T _A ≤ +105°C | |
| SID.GIO#17 | T _{FALLF} | Fall time in Fast Strong mode | | | | | | |
| SID.GIO#18 | T _{RISES} | Rise time in Slow Strong mode | 10 | | 60 | | | |
| SID.GIO#19 | T _{FALLS} | Fall time in Slow Strong mode | | | | | | |
| SID.GIO#20 | F _{GPIO_OUT1} | GPIO F _{OUT} ; 3.0 V ≤ V _{DD} ≤ 5.5 V. Fast Strong mode. | – | | 16 | MHz | | |
| SID.GIO#21 | F _{GPIO_OUT2} | GPIO F _{OUT} ; 3.0 V ≤ V _{DD} ≤ 5.5 V. Slow Strong mode. | | | 7 | | | |
| SID.GIO#22 | F _{GPIO_IN} | GPIO input operating frequency; 3.0 V ≤ V _{DD} ≤ 5.5 V. | | | 16 | | | –40°C ≤ T _A ≤ +105°C |

Table 14 GPIO OVT DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|-----------------------|---------------------|--|------------------------|-----|-----|------|--|
| SID.GPIO_20VT_GIO #4 | GPIO_20VT_I_LU | GPIO_20VT latch up current limits | –140 | – | 140 | mA | Max / Min current in to any input or output, pin-to-pin, pin-to-supply |
| SID.GPIO_20VT_GIO #5 | GPIO_20VT_RPU | GPIO_20VT pull-up resistor value | 3.5 | | 8.5 | kΩ | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID.GPIO_20VT_GIO #6 | GPIO_20VT_RPD | GPIO_20VT pull-down resistor value | | | | | |
| SID.GPIO_20VT_GIO #16 | GPIO_20VT_IIL | GPIO_20VT input leakage current (absolute value) | – | | 2 | nA | +25°C T _A , 3-V V _{DDD} |
| SID.GPIO_20VT_GIO #17 | GPIO_20VT_CPIN | GPIO_20VT pin capacitance | | | 10 | pF | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID.GPIO_20VT_GIO #33 | GPIO_20VT_Voh | GPIO_20VT output voltage high level. | V _{DDD} – 0.6 | | – | V | I _{OH} = –4 mA |
| SID.GPIO_20VT_GIO #36 | GPIO_20VT_Vol | GPIO_20VT output voltage low level. | – | | 0.6 | | I _{OL} = 8 mA |
| SID.GPIO_20VT_GIO #41 | GPIO_20VT_Vih_LVTTL | GPIO_20VT LVTTL input | 2 | | – | | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID.GPIO_20VT_GIO #42 | GPIO_20VT_Vil_LVTTL | GPIO_20VT LVTTL input | – | | 0.8 | | |
| SID.GPIO_20VT_GIO #43 | GPIO_20VT_Vhysttl | GPIO_20VT input hysteresis LVTTL | 100 | | – | – | mV |
| SID.GPIO_20VT_GIO #45 | GPIO_20VT_ITOT_GPIO | GPIO_20VT maximum total sink pin current to ground | – | – | 95 | mA | V(GPIO_20VT Pin) > V _{DDD} |

Table 15 GPIO OVT AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|-----------------------|-----------------------|---|-----|-----|-----|------|---|
| SID.GPIO_20VT_70 | GPIO_20VT_TriseF | GPIO_20VT rise time in Fast Strong Mode | 1 | – | 15 | ns | All V _{DD} , C _{load} = 25 pF |
| SID.GPIO_20VT_71 | GPIO_20VT_TfallF | GPIO_20VT fall time in Fast Strong Mode | | | | | |
| SID.GPIO_20VT_GPIO#46 | GPIO_20VT_TriseS | GPIO_20VT rise time in Slow Strong Mode | 10 | | 70 | | |
| SID.GPIO_20VT_GPIO#47 | GPIO_20VT_TfallS | GPIO_20VT fall time in Slow Strong Mode | | | | | |
| SID.GPIO_20VT_GPIO#48 | GPIO_20VT_FGPI-O_OUT1 | GPIO_20VT GPIO Fout; 3 V ≤ V _{DD} ≤ 5.5 V. Fast Strong mode. | – | | 33 | MHz | |
| SID.GPIO_20VT_GPIO#50 | GPIO_20VT_FGPI-O_OUT3 | GPIO_20VT GPIO Fout; 3 V≤V _{DD} ≤5.5V. Slow Strong mode. | | | 7 | | |
| SID.GPIO_20VT_GPIO#52 | GPIO_20VT_FG-PIO_IN | GPIO_20VT GPIO input operating frequency; 3 V ≤ V _{DD} ≤ 5.5 V | | | 8 | | All V _{DD} |

6.2.4 XRES

Table 16 XRES DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|------------|----------------|--|---------------------|----------------------|---------------------|------|------------------------|
| SID.XRES#1 | V_{IH_XRES} | Input voltage HIGH threshold on XRES pin | $0.7 \times V_{DD}$ | – | – | V | CMOS input |
| SID.XRES#2 | V_{IL_XRES} | Input voltage LOW threshold on XRES pin | – | | $0.3 \times V_{DD}$ | | |
| SID.XRES#3 | C_{IN_XRES} | Input capacitance on XRES pin | | | 7 | pF | – |
| SID.XRES#4 | $V_{HYSXRES}$ | Input voltage hysteresis on XRES pin | | $0.05 \times V_{DD}$ | – | mV | |

6.3 Digital peripherals

The following specifications apply to the Timer/Counter/PWM peripherals in the Timer mode.

6.3.1 PWM for GPIO pins

Table 17 PWM AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-------------|-----------------------|----------------------------|------------------|-----|----------------|------|--|
| SID.TCPWM.1 | TCPWM _{FREQ} | Operating frequency | – | – | F _c | MHz | F _c max = CLK_SYS |
| SID.TCPWM.3 | T _{PWMEXT} | Output trigger pulse width | 2/F _c | – | – | ns | Minimum possible width of overflow, underflow, and CC (counter equals compare value) outputs |
| SID.TCPWM.4 | T _{CRES} | Resolution of counter | 1/F _c | | | | Minimum time between successive counts |
| SID.TCPWM.5 | PWM _{RES} | PWM resolution | | | | | Minimum pulse width of PWM output |

6.3.2 I²C

Table 18 Fixed I²C AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|-------------------|-------------|-----|-----|-----|------|--------------------|
| SID153 | F _{I2C1} | Bit rate | – | – | 1 | Mbps | – |

6.3.3 UART

Table 19 Fixed UART AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|-------------------|-------------|-----|-----|-----|------|--------------------|
| SID162 | F _{UART} | Bit rate | – | – | 1 | Mbps | – |

6.3.4 SPI

Table 20 Fixed SPI AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|------------------|---|-----|-----|-----|------|--------------------|
| SID166 | F _{SPI} | SPI operating frequency (Master; 6X oversampling) | – | – | 8 | MHz | – |

Table 21 Fixed SPI Master mode AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|------------------|---|-----|-----|-----|------|----------------------------------|
| SID167 | T _{DMO} | MOSI valid after SClock driving edge | – | – | 15 | ns | – |
| SID168 | T _{DSI} | MISO valid before SClock capturing edge | 20 | | – | | Full clock, late MISO sampling |
| SID169 | T _{HMO} | Previous MOSI data hold time | 0 | | | | Referred to slave capturing edge |

Table 22 Fixed SPI Slave mode AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|---------|----------------------|---|-----|-----|------------------------------|------|---------------------------------------|
| SID170 | T _{DMI} | MOSI valid before Scklock capturing edge | 40 | – | – | ns | – |
| SID171 | T _{DSO} | MISO valid after Scklock driving edge | – | | 48 + (3 × T _{CPU}) | | T _{CPU} = 1/F _{CPU} |
| SID171A | T _{DSO_EXT} | MISO valid after Scklock driving edge in Ext Clk mode | | | 48 | | – |
| SID172 | T _{HSO} | Previous MISO data hold time | 0 | | – | | |
| SID172A | T _{SSELSCK} | SSEL valid to first SCK Valid edge | 100 | | | | |

6.3.5 Memory

Table 23 Flash AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|-----------|-----------------|---|------|-----|------|--------|---|
| SID.MEM#2 | FLASH_WRITE | Row (Block) write time (erase and program) | – | – | 20 | ms | $-40^{\circ}\text{C} \leq T_A \leq +85^{\circ}\text{C}$, All V_{DD} |
| SID.MEM#1 | FLASH_ERASE | Row erase time | | | 15.5 | | |
| SID.MEM#5 | FLASH_ROW_PGM | Row program time after erase | | | 7 | | |
| SID178 | $T_{BULKERASE}$ | Bulk erase time (32 KB) | | | 35 | s | – |
| SID180 | $T_{DEVPROG}$ | Total device program time | | | 7.5 | | |
| SID.MEM#6 | FLASH_ENPB | Flash write endurance | 100k | – | – | cycles | $25^{\circ}\text{C} \leq T_A \leq 55^{\circ}\text{C}$, All V_{DD} |
| SID182 | F_{RET1} | Flash retention, $T_A \leq 55^{\circ}\text{C}$, 100K P/E cycles | 20 | | | years | – |
| SID182A | F_{RET2} | Flash retention, $T_A \leq 85^{\circ}\text{C}$, 10K P/E cycles | 10 | | | | |

Electrical specifications

6.4 System resources

6.4.1 Power-on-reset (POR) with brown out

Table 24 Imprecise power-on reset (IPOR)

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|-----------------------|--|------|-----|------|------|--|
| SID185 | V _{RISEIPOR} | Power-on reset (POR) rising trip voltage | 0.80 | – | 1.50 | V | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID186 | V _{FALLIPOR} | POR falling trip voltage | 0.70 | | 1.4 | | |

Table 25 Precise POR

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|------------------------|---|------|-----|------|------|--|
| SID190 | V _{FALLPPOR} | Brown-out detect (BOD) trip voltage in Active/Sleep modes | 1.48 | – | 1.62 | V | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID192 | V _{FALLDPSLP} | BOD trip voltage in Deep Sleep mode | 1.1 | | 1.5 | | |

6.4.2 SWD interface

Table 26 SWD interface specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions | |
|-----------|--------------|---|----------|-----|----------|------|--------------------|--|
| SID.SWD#1 | F_SWDC1K1 | $3.0\text{ V} \leq V_{\text{DDIO}} \leq 5.5\text{ V}$ | – | – | 14 | MHz | – | |
| SID.SWD#2 | T_SWDI_SETUP | T = 1/f SWDC1K | 0.25 × T | | – | ns | | |
| SID.SWD#3 | T_SWDI_HOLD | | | | – | | | |
| SID.SWD#4 | T_SWDO_VALID | | | | 0.50 × T | | | |
| SID.SWD#5 | T_SWDO_HOLD | | | | – | | | |

6.4.3 IMO

Table 27 IMO AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|-----------------------|---|-----|-----|-----|------|---|
| SID.CLK#13 | F _{IMOTOL} | Frequency variation at 48 MHz (trimmed) | – | – | ±2 | % | 3.0 V ≤ V _{DDD} < 5.5 V. –40°C ≤ T _A ≤ 105°C |
| SID226 | T _{STARTIMO} | IMO start-up time | | | 7 | μs | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID.CLK#1 | F _{IMO} | IMO frequency | 24 | | 48 | MHz | |

6.4.4 Internal low-speed oscillator

Table 28 ILO AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------|------------------------|-------------------|-----|-----|-----|------|--|
| SID234 | T _{STARTILO1} | ILO start-up time | – | – | 2 | ms | –40°C ≤ T _A ≤ +105°C, All V _{DDD} |
| SID238 | T _{ILODUTY} | ILO duty cycle | 40 | 50 | 60 | % | |
| SID.CLK#5 | F _{ILO} | ILO frequency | 20 | 40 | 80 | kHz | – |

6.4.5 PD

Table 29 PD DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/ conditions |
|-------------------|------------------|--|------|-----|-------|------|------------------------|
| SID.DC.cc_shvt.1 | vSwing | Transmitter output High Voltage | 1.05 | – | 1.2 | V | – |
| SID.DC.cc_shvt.2 | vSwing_low | Transmitter output Low Voltage | – | | 0.075 | | |
| SID.DC.cc_shvt.3 | zDriver | Transmitter output impedance | 33 | | 75 | Ω | |
| SID.DC.cc_shvt.4 | zBmcRx | Receiver input impedance | 10 | | – | MΩ | |
| SID.DC.cc_shvt.5 | Idac_std | Source current for USB standard advertisement | 64 | | 96 | μA | |
| SID.DC.cc_shvt.6 | Idac_1p5a | Source current for 1.5 A at 5 V advertisement | 166 | | 194 | | |
| SID.DC.cc_shvt.7 | Idac_3a | Source current for 3 A at 5 V advertisement | 304 | | 356 | | |
| SID.DC.cc_shvt.8 | Rd | Pull down termination resistance when acting as upstream facing port (UFP) | 4.59 | | 5.61 | kΩ | |
| SID.DC.cc_shvt.10 | zOPEN | CC impedance to ground when disabled | 108 | | – | | |
| SID.DC.cc_shvt.11 | DFP_default_0p2 | CC voltages on DFP side-standard USB | 0.15 | | 0.25 | V | |
| SID.DC.cc_shvt.12 | DFP_1.5A_0p4 | CC voltages on DFP side-1.5A | 0.35 | | 0.45 | | |
| SID.DC.cc_shvt.13 | DFP_3A_0p8 | CC voltages on DFP side-3 A | 0.75 | | 0.85 | | |
| SID.DC.cc_shvt.14 | DFP_3A_2p6 | CC voltages on DFP side-3 A | 2.45 | | 2.75 | | |
| SID.DC.cc_shvt.15 | UFP_default_0p66 | CC voltages on UFP side-Standard USB | 0.61 | | 0.7 | | |
| SID.DC.cc_shvt.16 | UFP_1.5A_1p23 | CC voltages on UFP side-1.5A | 1.16 | | 1.31 | | |
| SID.DC.cc_shvt.17 | Vattach_ds | Deep sleep attach threshold | 0.3 | | 0.6 | % | |
| SID.DC.cc_shvt.18 | Rattach_ds | Deep sleep pull-up resistor | 10 | | 50 | kΩ | |
| SID.DC.cc_shvt.19 | VTX_step | TX drive voltage step size | 80 | | 120 | mV | |

6.4.6 Analog-to-digital converter

Table 30 ADC DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------|------------|----------------------------|-------------|-----|-------------|------|---|
| SID.ADC.1 | Resolution | ADC resolution | – | 8 | – | Bits | – |
| SID.ADC.2 | INL | Integral non-linearity | –1.5 | – | 1.5 | LSB | Reference voltage generated from bandgap |
| SID.ADC.3 | DNL | Differential non-linearity | –2.5 | | 2.5 | | Reference voltage generated from V_{DD} |
| SID.ADC.4 | Gain Error | Gain error | –1.5 | | 1.5 | | Reference voltage generated from bandgap |
| SID.ADC.5 | VREF_ADC1 | Reference voltage of ADC | V_{DDmin} | | V_{DDmax} | V | Reference voltage generated from V_{DD} |
| SID.ADC.6 | VREF_ADC2 | Reference voltage of ADC | 1.96 | 2.0 | 2.04 | | Reference voltage generated from deep sleep reference |

6.4.7 High-side CSA

Table 31 High-side CSA DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|--------------|--------------|--|-----|-----|-----|------|--------------------|
| SID.HSCSA.1 | Csa_Acc1 | CSA accuracy 5 mV < Vsense < 10 mV | –15 | – | 15 | % | Active mode |
| SID.HSCSA.2 | Csa_Acc2 | CSA accuracy 10 mV < Vsense < 15 mV | –10 | | 10 | | |
| SID.HSCSA.3 | Csa_Acc3 | CSA accuracy 15 mV < Vsense < 25 mV | –5 | | 5 | | |
| SID.HSCSA.4 | Csa_Acc4 | CSA accuracy 25 mV < Vsense | –3 | | 3 | | |
| SID.HSCSA.7 | Csa_SCP_Acc1 | CSA SCP at 6 A with 5-mΩ sense resistor | –10 | | 10 | | |
| SID.HSCSA.8 | Csa_SCP_Acc2 | CSA SCP at 10 A with 5-mΩ sense resistor | –10 | | 10 | | |
| SID.HSCSA.9 | Csa_OCP_1A | CSA OCP at 1 A with 5-mΩ sense resistor | 104 | 130 | 156 | | |
| SID.HSCSA.10 | Csa_OCP_5A | CSA OCP for 5 A with 5-mΩ sense resistor | 123 | 130 | 137 | | |

Electrical specifications

Table 32 High-side CSA AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|----------------|-------------------------|--|-----|-----|-----|------|--------------------|
| SID.HSCSA.AC.1 | T _{SCP_GATE} | Delay from SCP threshold trip to external NFET power gate turn off | – | 3.5 | – | μs | 1 nF NFET gate |
| SID.HSCSA.AC.2 | T _{SCP_GATE_1} | Delay from SCP threshold trip to external NFET power gate turn off | | 8 | | | 3 nF NFET gate |

6.4.8 UV/OV

Table 33 UV/OV Specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|-----------|--|------|-----|-----|------|--------------------|
| SID.UVOV.1 | VTHOV1 | Overvoltage threshold Accuracy, 4 V to 11 V | –3 | – | 3 | % | Active mode |
| SID.UVOV.2 | VTHOV2 | Overvoltage threshold Accuracy, 11 V to 21.5 V | –3.2 | | 3.2 | | |
| SID.UVOV.3 | VTHUV1 | Undervoltage threshold Accuracy, 3 V to 3.3 V | –4 | | 4 | | |
| SID.UVOV.4 | VTHUV2 | Undervoltage threshold Accuracy, 3.3 V to 4.0 V | –3.5 | | 3.5 | | |
| SID.UVOV.5 | VTHUV3 | Undervoltage threshold Accuracy, 4.0 V to 21.5 V | –3 | | 3 | | |

6.4.9 VCONN switch

Table 34 VCONN switch DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|-------------------|--|------|-----|------|------|--------------------|
| DC.VCONN.1 | VCONN_OUT | VCONN output voltage with 20 mA load current | 4.5 | – | 5.5 | V | – |
| DC.VCONN.2 | I _{LEAK} | Connector side pin leakage current | – | | 10 | μA | |
| DC.VCONN.3 | I _{OC} P | VCONN Over-Current Protection Threshold | 22.5 | | 42.5 | mA | |

Table 35 VCONN switch AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|------------------|----------------------------|-----|-----|-----|------|--------------------|
| AC.VCONN.1 | T _{ON} | VCONN switch turn-on time | – | – | 600 | μs | – |
| AC.VCONN.2 | T _{OFF} | VCONN switch turn-off time | | | 10 | | |

6.4.10 V_{BUS}

Table 36 V_{BUS} discharge specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------------|-----------------|---|-------|-----|------|----------|--------------------------------|
| SID.VBUS.DISC.1 | R1 | 20-V NMOS ON resistance for DS = 1 | 500 | – | 2000 | Ω | Measured at 0.5 V |
| SID.VBUS.DISC.2 | R2 | 20-V NMOS ON resistance for DS = 2 | 250 | | 1000 | | |
| SID.VBUS.DISC.3 | R4 | 20-V NMOS ON resistance for DS = 4 | 125 | | 500 | | |
| SID.VBUS.DISC.4 | R8 | 20-V NMOS ON resistance for DS = 8 | 62.5 | | 250 | | |
| SID.VBUS.DISC.5 | R16 | 20-V NMOS ON resistance for DS = 16 | 31.25 | | 125 | | |
| SID.VBUS.DISC.6 | Vbus_stop_error | Error percentage of final VBUS value from setting | – | | 10 | % | When VBUS is discharged to 5 V |

6.4.11 Voltage regulation

Table 37 Voltage regulation DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-------------|-----------|--|-----|---------|---------|------|--------------------|
| SID.DC.VR.1 | VOUT | VBUS_IN output voltage range | 3.3 | – | 21.5 | V | – |
| SID.DC.VR.2 | VR | VBUS_IN voltage regulation accuracy | – | ± 3 | ± 5 | % | |
| SID.DC.VR.3 | VIN_UVLO | VIN Supply below which chip will get reset | 1.7 | – | 3.0 | V | |

Table 38 Voltage regulator specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|------------|--------------------|---|-----|-----|-----|---------------|--------------------|
| SID.VREG.1 | T _{START} | Total startup time for the regulator supply outputs | – | – | 200 | μs | – |

6.4.12 VBUS gate driver

Table 39 VBUS gate driver DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|----------|-----------|--|-----|-----|------|------|---|
| SID.GD.1 | GD_VGS | Gate to source overdrive during ON condition | 4.5 | 5 | 10 | V | NFET driver is ON. |
| SID.GD.2 | GD_RPD | Resistance when pull-down enabled | – | – | 2 | kΩ | Applicable on VBUS_CTRL to turn off external NFET |
| SID.GD.5 | GD_drv | Programmable typical gate current | 0.3 | | 9.75 | μA | – |

Table 40 VBUS gate driver AC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|----------|------------------|--|-----|-----|-----|------|------------------------------|
| SID.GD.3 | T _{ON} | VBUS_CTRL Low to High (1 V to VBUS + 1 V) with 3 nF external capacitance | 2 | 5 | 10 | ms | V _{BUS_IN} = 5 V |
| SID.GD.4 | T _{OFF} | VBUS_CTRL High to Low (90% to 10%) with 3 nF external capacitance | – | 7 | – | μs | V _{BUS_IN} = 21.5 V |

6.4.13 PWM controller

Table 41 Buck-boost PWM controller specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|-----------------|--|-----|------|-----|------|--------------------|
| PWM.1 | F _{SW} | Switching frequency | 150 | – | 600 | kHz | – |
| PWM.2 | FSS | Spread spectrum frequency dithering span | – | 10 | – | % | |
| PWM.3 | Ratio_Buck_BB | Buck to buck boost ratio | | 1.16 | – | | |
| PWM.4 | Ratio_Boost_BB | Boost to buck boost ratio | | 0.84 | | | |

6.4.14 NFET gate driver

Table 42 Buck-boost NFET gate driver specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|---------|-----------|--|-----|-----|-----|------|--------------------|
| DR.1 | R_HS_PU | Top-side gate driver on-resistance - gate pull-up | – | 2 | – | Ω | – |
| DR.2 | R_HS_PD | Top-side gate driver on-resistance - gate pull-down | | 1.5 | | | |
| DR.3 | R_LS_PU | Bottom-side gate driver on-resistance - gate pull-up | | 2 | | | |
| DR.4 | R_LS_PD | Bottom-side gate driver on-resistance - gate pull-down | | 1.5 | | | |
| DR.5 | Dead_HS | Dead time before high-side rising edge | | 30 | | ns | |
| DR.6 | Dead_LS | Dead time before low-side rising edge | | 30 | | | |
| DR.7 | Tr_HS | Top-side gate driver rise time | | 25 | | | |
| DR.8 | Tf_HS | Top-side gate driver fall time | | 20 | | | |
| DR.9 | Tr_LS | Bottom-side gate driver rise time | | 25 | | | |
| DR.10 | Tf_LS | Bottom-side gate driver fall time | | 20 | | | |

6.4.15 LS-SCP

Table 43 LS-SCP DC specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------------|------------|-------------------------------------|-----|-----|------|------|--|
| SID.LSSCP.DC.1 | SCP_6A | Short circuit current detect at 6A | 5.4 | 6 | 6.6 | A | Using differential inputs (CSN_1_GPIO12, CSP_1_GPIO13 or CSP_0_GPIO0, CSN_0_GPIO1) |
| SID.LSSCP.DC.1A | SCP_6A_SE | Short circuit current detect at 6A | 4.5 | 6 | 7.5 | | Using single ended inputs (CSP_1_GPIO13 or CSP_0_GPIO0) and internal ground |
| SID.LSSCP.DC.2 | SCP_10A | Short circuit current detect at 10A | 9 | 10 | 11 | | Using differential inputs (CSN_1_GPIO12, CSP_1_GPIO13 or CSP_0_GPIO0, CSN_0_GPIO1) |
| SID.LSSCP.DC.2A | SCP_10A_SE | Short circuit current detect at 10A | 7.5 | 10 | 12.5 | | Using single ended inputs (CSP_1_GPIO13 or CSP_0_GPIO0) and internal ground |

6.4.16 Thermal

Table 44 Thermal specifications

| Spec ID | Parameter | Description | Min | Typ | Max | Unit | Details/conditions |
|-----------|-----------|------------------|-----|-----|-----|------|--------------------|
| SID.OTP.1 | OTP | Thermal shutdown | 120 | 125 | 130 | °C | – |

7 Ordering information

Table 45 lists the EZ-PD™ CCG7D part numbers and features.

Table 45 EZ-PD™ CCG7D ordering Information

| Product | Application | Termination resistor | Role | Switching frequency | Package type |
|------------------|---------------------------------|----------------------|-------------------------|---------------------|--------------|
| CYPD7291-68LDXS | Rear seat and head unit charger | R _p | DFP (power source only) | 150 to 600 kHz | 68-pin QFN |
| CYPD7291-68LDXST | | | DFP power, UFP data | | |
| CYPD7299-68LDXS | Rear seat entertainment | | | | |
| CYPD7299-68LDXST | | | | | |

7.1 Ordering code definitions

| | | | | | | | | | | | |
|----|----|---|---|----|---|----|----|---|---|---|---|
| CY | PD | X | X | XX | - | XX | XX | X | X | X | |
| | | | | | | | | | | | T = Tape and reel (optional) |
| | | | | | | | | | | | Temperature grade: S = Automotive grade |
| | | | | | | | | | | | Lead: X = Pb-free |
| | | | | | | | | | | | Package type: LD = QFN wettable flank |
| | | | | | | | | | | | Number of pins in the package |
| | | | | | | | | | | | Application and feature combination designation |
| | | | | | | | | | | | Number of Type-C Ports: 1 = 1 Port, 2 = 2 Port |
| | | | | | | | | | | | Product type: 7 = Seventh-generation product family |
| | | | | | | | | | | | Marketing code: PD = Power Delivery product family |
| | | | | | | | | | | | Company ID: CY = Cypress (an Infineon company) |

8 Packaging

Table 46 Package characteristics

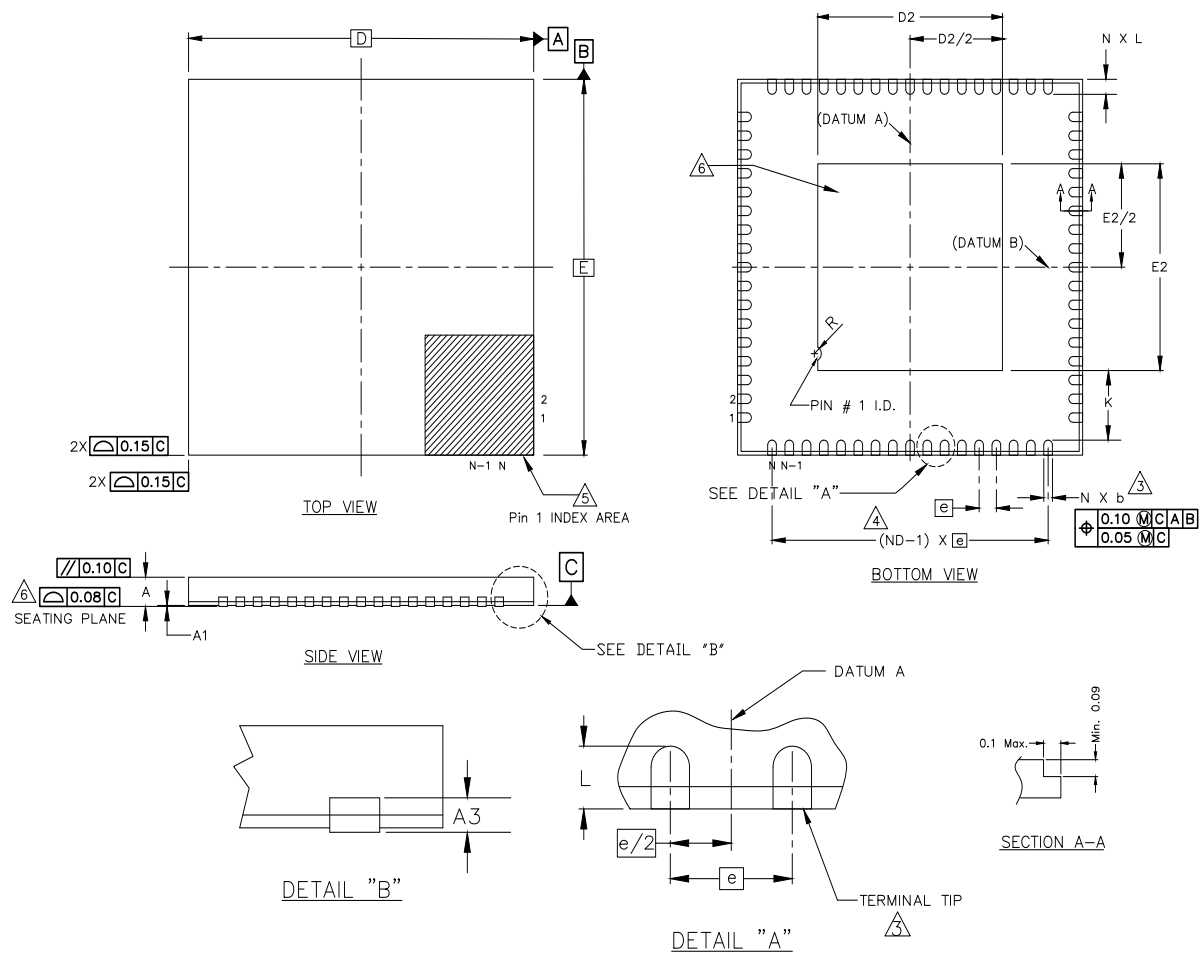
| Parameter | Description | Conditions | Min | Typ | Max | Unit |
|-----------------|--------------------------------|------------|-----|-----|------|------|
| T _J | Operating junction temperature | – | –40 | 25 | 125 | °C |
| T _{JA} | Package θ_{JA} | | – | – | 12.1 | °C/W |
| T _{JC} | Package θ_{JC} | | | | 3.1 | |

Table 47 Solder reflow peak temperature

| Package | Maximum peak temperature | Maximum time within 5°C of peak temperature |
|---------|--------------------------|---|
| 68-QFN | 260°C | 30 seconds |

Table 48 Package moisture sensitivity level (MSL), IPC/JEDEC J-STD-2

| Package | MSL |
|---------|-------|
| 68-QFN | MSL 3 |



| SYMBOL | DIMENSIONS | | |
|--------|------------|------|------|
| | MIN. | NOM. | MAX. |
| e | 0.50 BSC | | |
| N | 68 | | |
| ND | 17 | | |
| L | 0.30 | 0.40 | 0.50 |
| b | 0.18 | 0.25 | 0.30 |
| D2 | 5.25 | 5.35 | 5.45 |
| E2 | 5.40 | 5.50 | 5.60 |
| D | 10.00 BSC | | |
| E | 10.00 BSC | | |
| A | - | - | 1.00 |
| A1 | 0.00 | - | 0.05 |
| A3 | 0.203 REF | | |
| R | 0.20 TYP | | |
| K | 0.35 MIN | | |

NOTES:

- ALL DIMENSIONS ARE IN MILLIMETERS.
- N IS THE TOTAL NUMBER OF TERMINALS.
- DIMENSION "b" APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL TIP. IF THE TERMINAL HAS THE OPTIONAL RADIUS ON THE OTHER END OF THE TERMINAL, THE DIMENSION "b" SHOULD NOT BE MEASURED IN THAT RADIUS AREA.
- ND REFERS TO THE NUMBER OF TERMINALS ON D SIDE.
- PIN #1 ID ON TOP WILL BE LOCATED WITHIN THE INDICATED ZONE.
- COPLANARITY ZONE APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.
- JEDEC SPECIFICATION NO. REF. : N/A.

002-29306 *A

Figure 18 68-lead QFN (10.0 10.0 1.0 mm), LV68A (5.35 5.50 mm) EPAD (SAWN) (wettable flank), (PG-VQFN-68)

Packaging

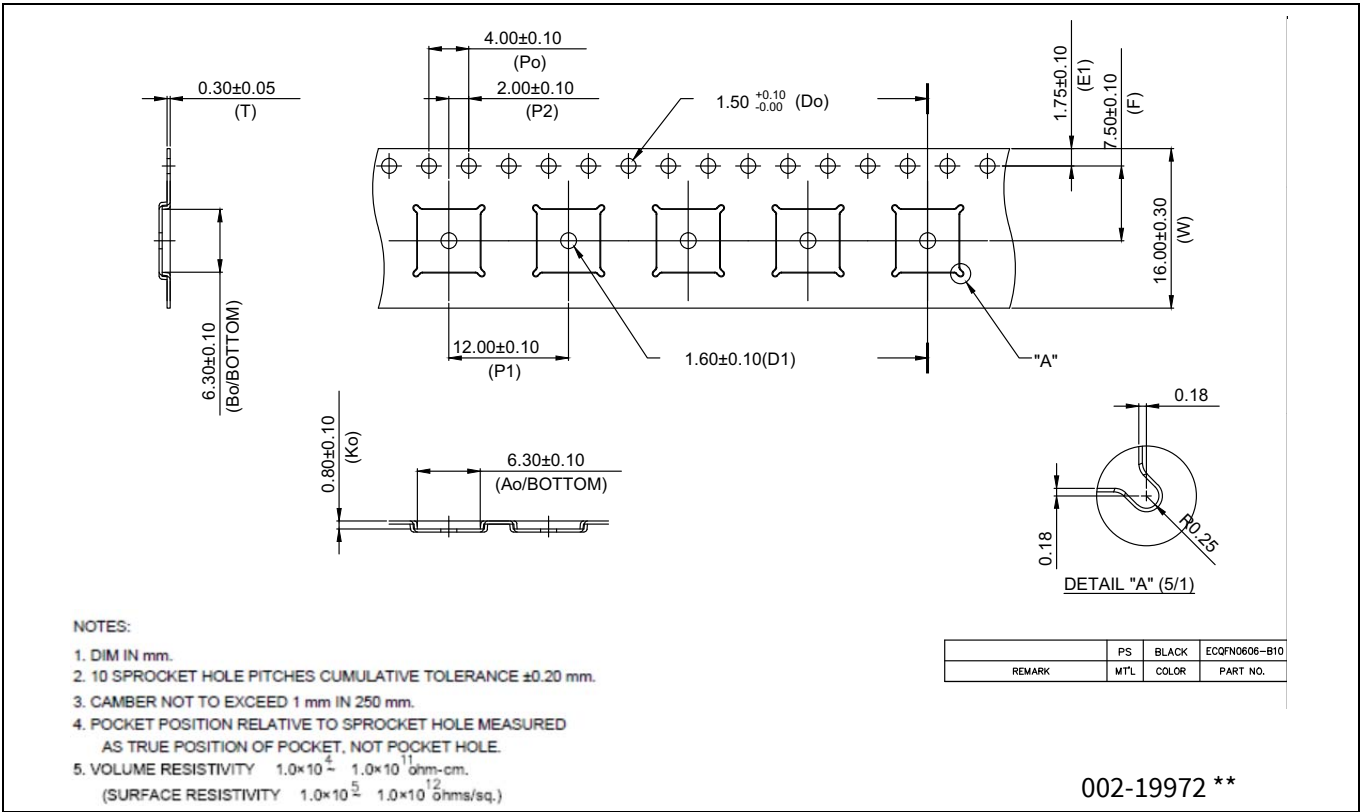


Figure 19 Carrier tape dimensions

9 Acronyms

Table 49 Acronyms used in this document

| Acronym | Description |
|--------------------------|---|
| ADC | analog-to-digital converter |
| AFC | Samsung Adaptive Fast Charging |
| Arm® | advanced RISC machine, a CPU architecture |
| BOD | brownout detect |
| BMC | biphase mark coding |
| CC | configuration channel |
| CDP | charging downstream port |
| CMOS | Complementary Metal Oxide Semiconductor |
| CPU | central processing unit |
| CSA | current sense amplifier |
| DAC | digital-to-analog converter |
| DCM | discontinuous-conduction mode |
| DFP | downstream facing port |
| EA | error amplifier |
| EMC | electromagnetic compatibility |
| EMCA | electronically marked cable assembly, a USB cable that includes an IC that reports cable characteristics (e.g., current rating) to the Type-C |
| EMI | electromagnetic interference |
| EPAD | exposed pad |
| ESD | electrostatic discharge |
| FCCM | forced continuous current/conduction mode |
| GPIO | general-purpose input/output |
| HPI | host processor interface |
| HSDR | high-side driver |
| HSIOM | high-speed I/O matrix |
| HU | head unit |
| HUC | head unit charger |
| I ² C, or IIC | inter-integrated circuit, a communications protocol |
| IDAC | current DAC |
| I/O | input/output, see also GPIO |
| ILO | internal low-speed oscillator |
| IMO | internal main oscillator |
| IRQ | interrupt request |
| ISR | interrupt service routine |
| LSDR | low-side driver |
| LVTTL | low-voltage transistor-transistor logic |
| MCU | microcontroller unit |
| NTC | negative temperature coefficient (refers to a thermistor) |

Acronyms

Table 49 **Acronyms used in this document** *(continued)*

| Acronym | Description |
|---------|--|
| OCP | overcurrent protection |
| OTP | overtemperature protection |
| OVP | overvoltage protection |
| PD | power delivery |
| POR | power-on reset |
| PPS | programmable power supply |
| PSOC™ | Programmable System-on-Chip™ |
| PSM | pulse-skipping mode |
| PWM | pulse-width modulator |
| RCP | reverse current protection |
| RAM | random-access memory |
| ROM | read-only memory |
| RSC | rear-seat charger |
| RSE | rear-seat entertainment |
| SCB | serial communications block |
| SPI | serial peripheral interface, a communications protocol |
| SRAM | static random access memory |
| SWD | serial wire debug, a test protocol |
| TCPWM | timer/counter/PWM |
| Type-C | a new standard with a slimmer USB connector and a reversible cable, capable of sourcing up to 100 W of power |
| UART | Universal Asynchronous Transmitter Receiver, a communications protocol |
| UFP | upstream facing port |
| UVP | undervoltage protection |
| USB | Universal Serial Bus |
| UVLO | undervoltage lockout |
| VPA | VCONN-powered accessories |
| VPD | VCONN-powered devices |
| WDT | watchdog timer |
| WIC | wakeup interrupt controller |
| ZCD | zero-crossing detector |

10 Document conventions

10.1 Units of measure

Table 50 Units of measure

| Symbol | Unit of measure |
|--------|------------------------|
| °C | degree celsius |
| Hz | hertz |
| KB | 1024 bytes |
| kHz | kilohertz |
| kΩ | kiloohm |
| Mbps | megabits per second |
| MHz | megahertz |
| MΩ | megaohm |
| Msps | megasamples per second |
| μA | microampere |
| μF | microfarad |
| μs | microsecond |
| μV | microvolt |
| μW | microwatt |
| mA | milliampere |
| mΩ | milliohm |
| ms | millisecond |
| mV | millivolt |
| nA | nanoampere |
| ns | nanosecond |
| Ω | ohm |
| pF | picofarad |
| ppm | parts per million |
| ps | picosecond |
| s | second |
| sps | samples per second |

Revision history

| Document revision | Date | Description of changes |
|-------------------|------------|--|
| *N | 2023-01-31 | Removed “restricted” status from the datasheet. Post to external web. |
| *O | 2025-01-31 | Updated USB PD revision number to ‘3.2’ across the document. Added Table 3 . Added Application firmware update using bootloader section. Updated Figure 16 and its associated Table 6 . Updated the maximum value of “DC.VCONN.3’ to ‘42.5 mA’ in Table 34 . Added ordering part numbers “CYPD7291-68LDXST” and “CYPD7299-68LDXST” in Table 45 . Updated document title. |

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